



# Wide band-gap semiconductor sensors and front-ends for harsh environments

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- SiC sensors for MIP detectors at COMET muon experiment @ J-PARC (Japan Proton Accelerator Research Complex)
  - Application to muon beam monitor and proton extinction monitor
  - Characteristics of the PN-sensors
- Diamond sensors for neutron detection at Fukushima nuclear power plant
  - Device fabrication and characteristics
  - Detector system and prototype performance



# Introduction

- SiC and diamond are more radiation-hard than standard n-type Si,  $10^{14}$   $n_{eq}/cm^2$  for SiC and  $10^{15}$   $n_{eq}/cm^2$  for diamond.
- Uniform device characteristics and productivity are still challenging.

Property	Diamond	GaN	4H-SiC	Si	Ge	CdTe	CdZnTe
$E_g$ [eV]	5.5	3.39	3.26	1.12	0.67	1.44	1.60
$E_{breakdown}$ [V/cm]	$10^7$	$4 \times 10^6$	$2.2 \times 10^6$	$3 \times 10^5$	$10^5$	TBD	TBD
$\mu_e$ [ $cm^2/Vs$ ]	1800	100	800	1450	<3900 <sup>[2]</sup>	1090 <sup>[1]</sup>	906 <sup>[3]</sup>
$\mu_h$ [ $cm^2/Vs$ ]	1200	30	115	450	<1900	110	-
$v_{sat}$ [cm/s]	$2.2 \times 10^7$	-	$2 \times 10^7$	$0.8 \times 10^7$	$0.74 \times 10^7$ <sup>[5]</sup>	$10^7$	$10^7$
Z	6	31/7	14/6	14	32	48/52	48/52/30
$\epsilon_r$ (dielectric const.)	5.7	9.6	9.7	11.7	TBD	TBD	TBD
e-h energy [eV]	13	8.9	7.6-8.4	3.6	2.9	4.5	5.0
Density	3.515	6.15	3.22	2.33	5.3	5.9	5.8
Displacem. [eV]	43	20	25	13-20	15-18	5.3-6.2 <sup>[4]</sup>	-

low leakage current

high radiation-tolerance

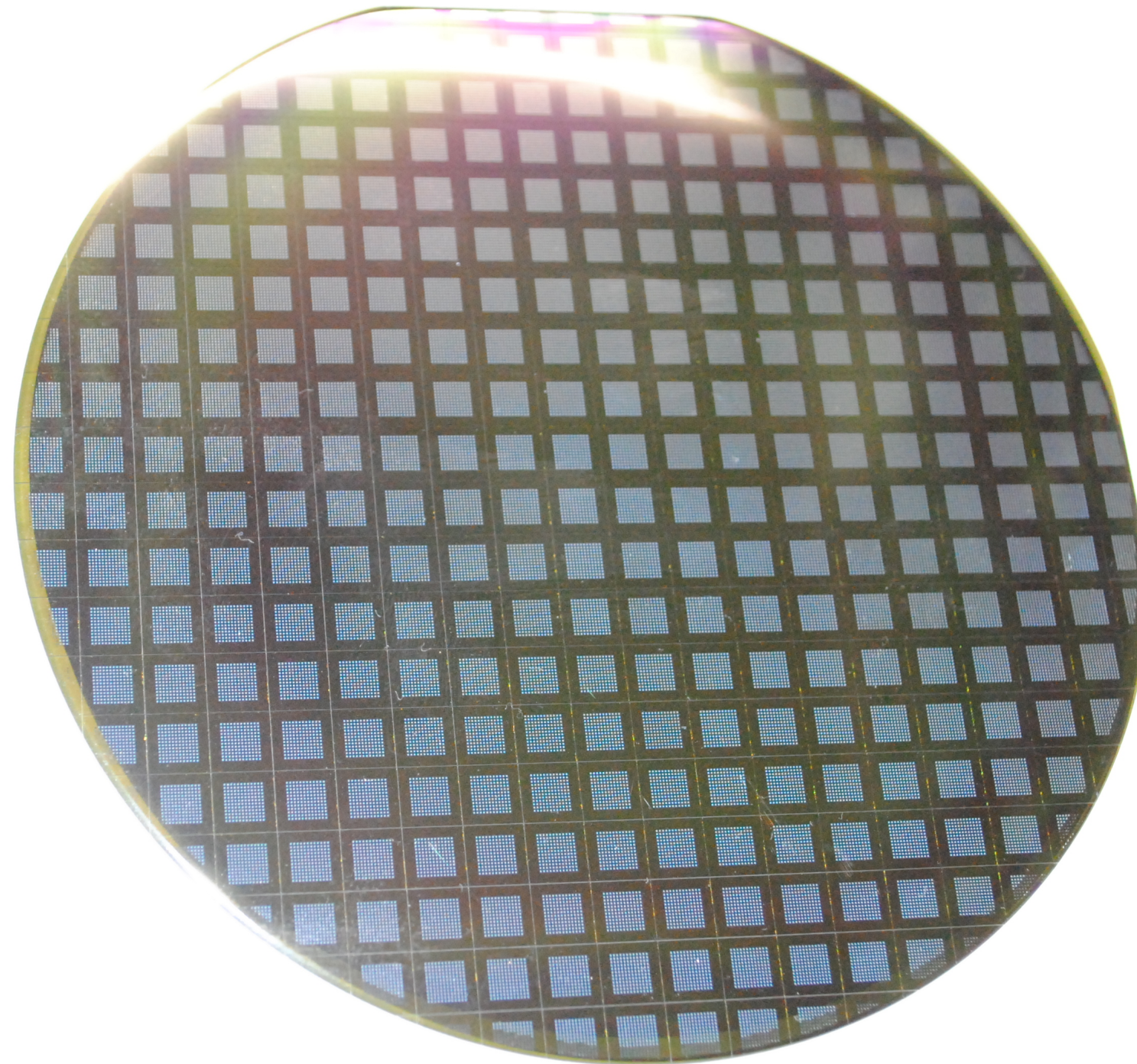
small signal charges

For stable device production, KEK-Esys collaborates with AIST power device group from 2019.



# SiC device fabrication

- **PN diodes in wafer process**
- Reverse bias tolerance of 3 kV
- 50  $\mu\text{m}$  epi grown on (0001) 4H-SiC n-type substrate @AIST
- Nd-Na:  $4.7 \times 10^{14} \text{ cm}^{-3}$
- Thickness: 350  $\mu\text{m}$
- 260 dies with  $5 \times 5 \text{ mm}^2$  from 4-inch wafer,  $4 \times 4 \text{ mm}^2$  active area



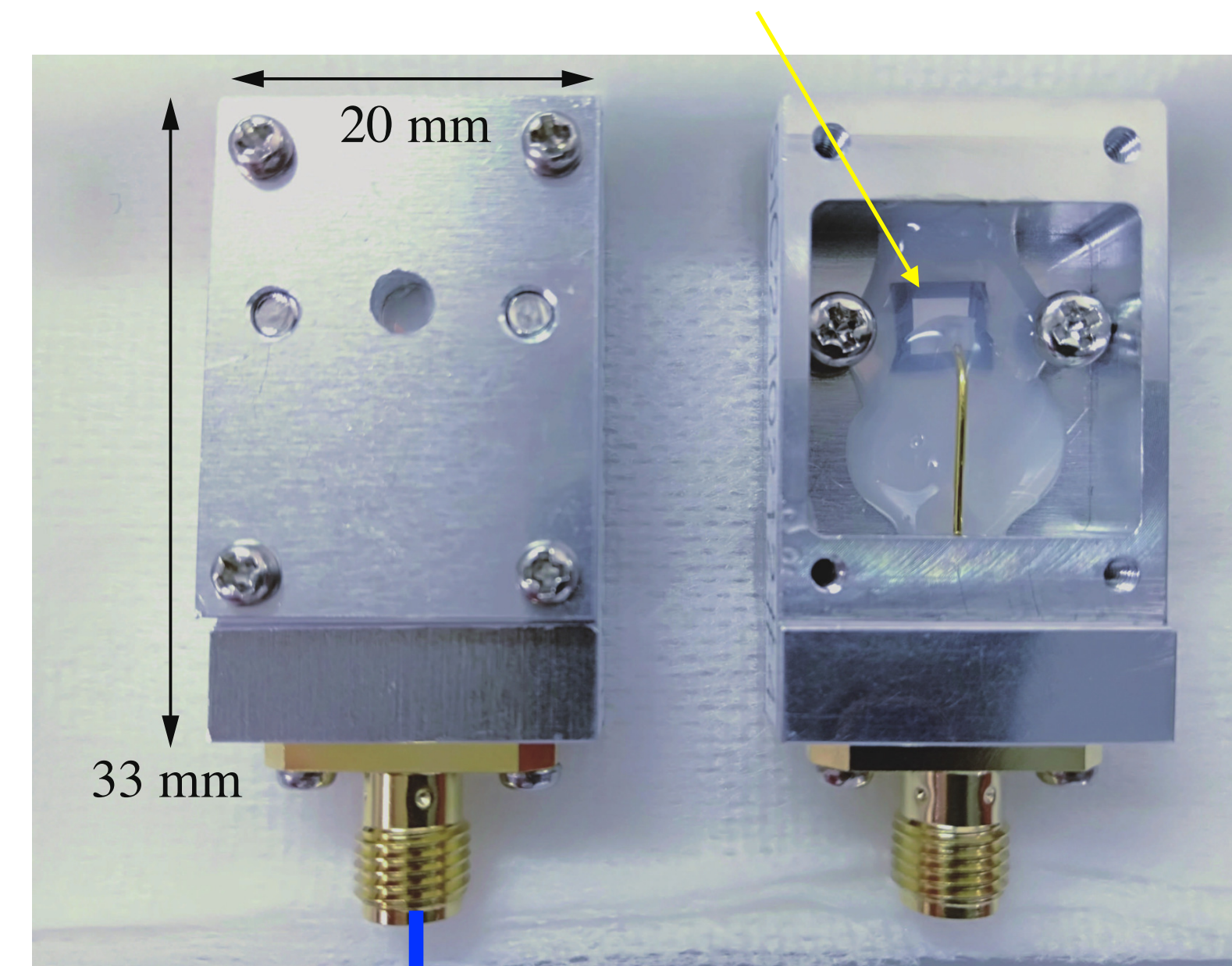
## Schottky diode

- Easy process
- Sensitive to surface conditions

## PN diode

- Difficult process  
(High temperature annealing)
- Less sensitive to surface conditions

Silicone rubber for preventing electric discharges

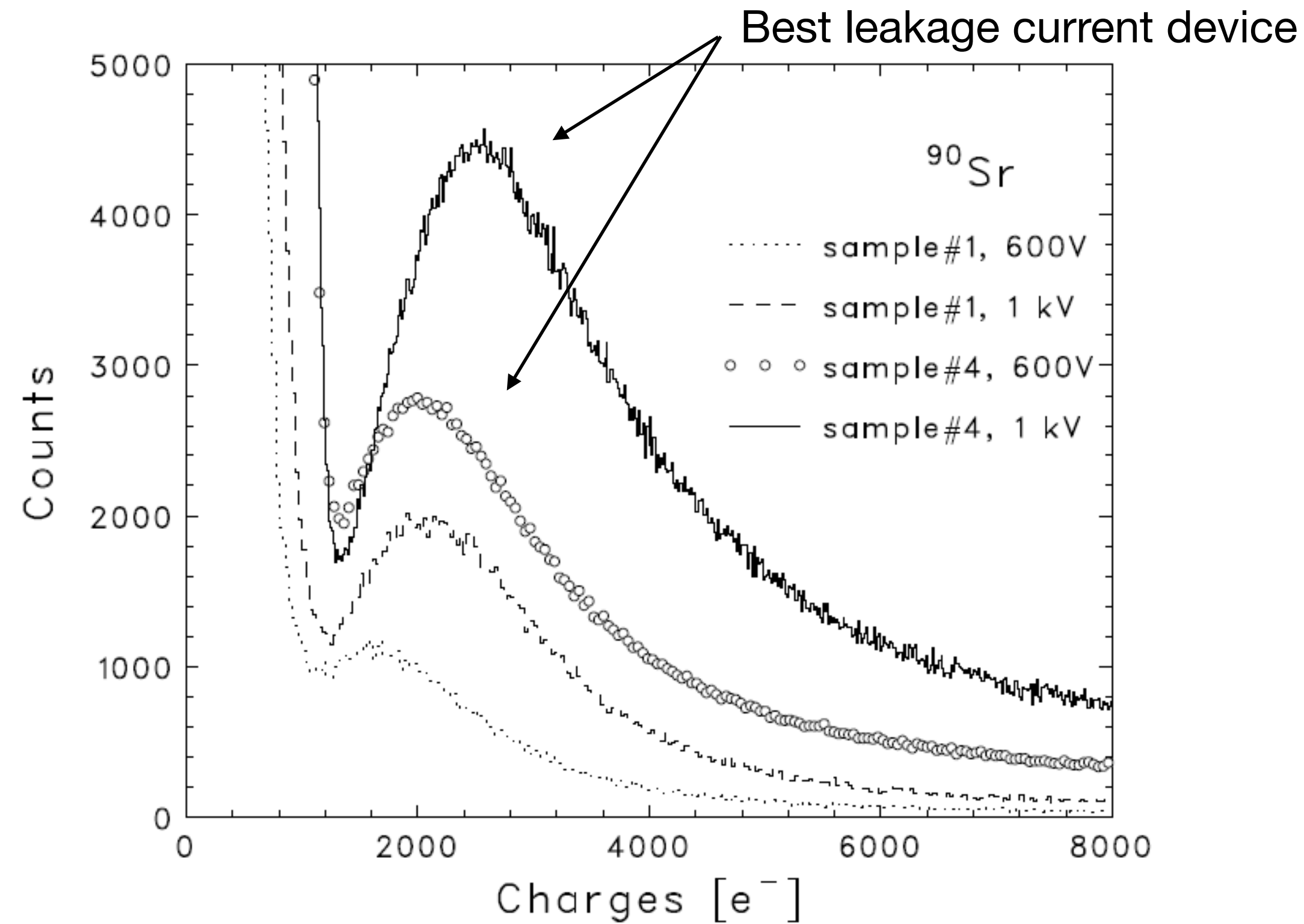


commercial CSA (AC-coupling)+shaper

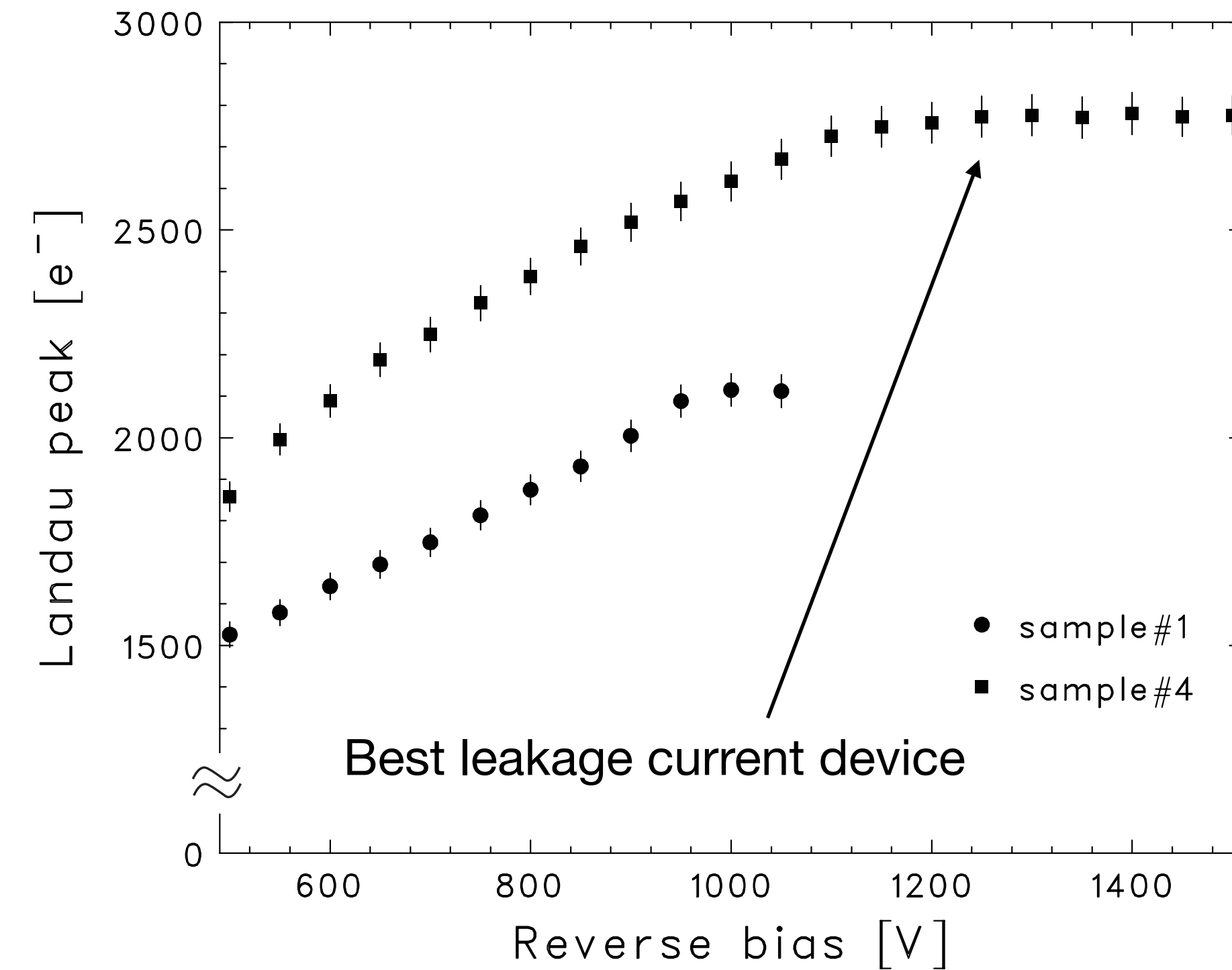


# Device characteristics

- Leakage current <10 nA (26 samples from 260 dies), uniform within one order of magnitude
- Stable Landau peak position (no polarization/charge-up)
- Full depletion voltage 1000 V for 50 um epi (TCAD).



Landau peak is separated from pedestal in worst leakage device.



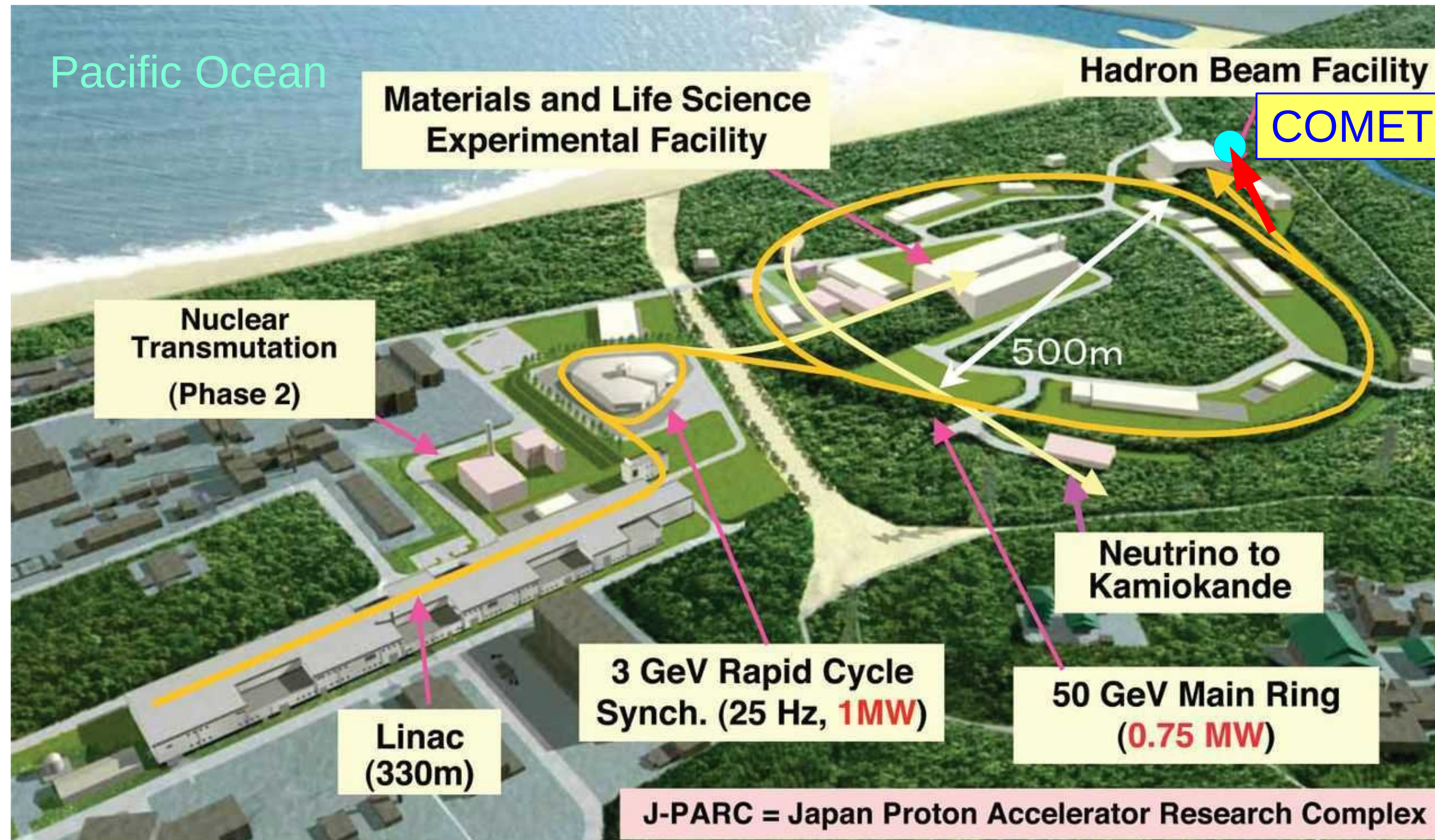
Full-depletion voltage is consistent with TCAD simulation.

What can we do with these devices?



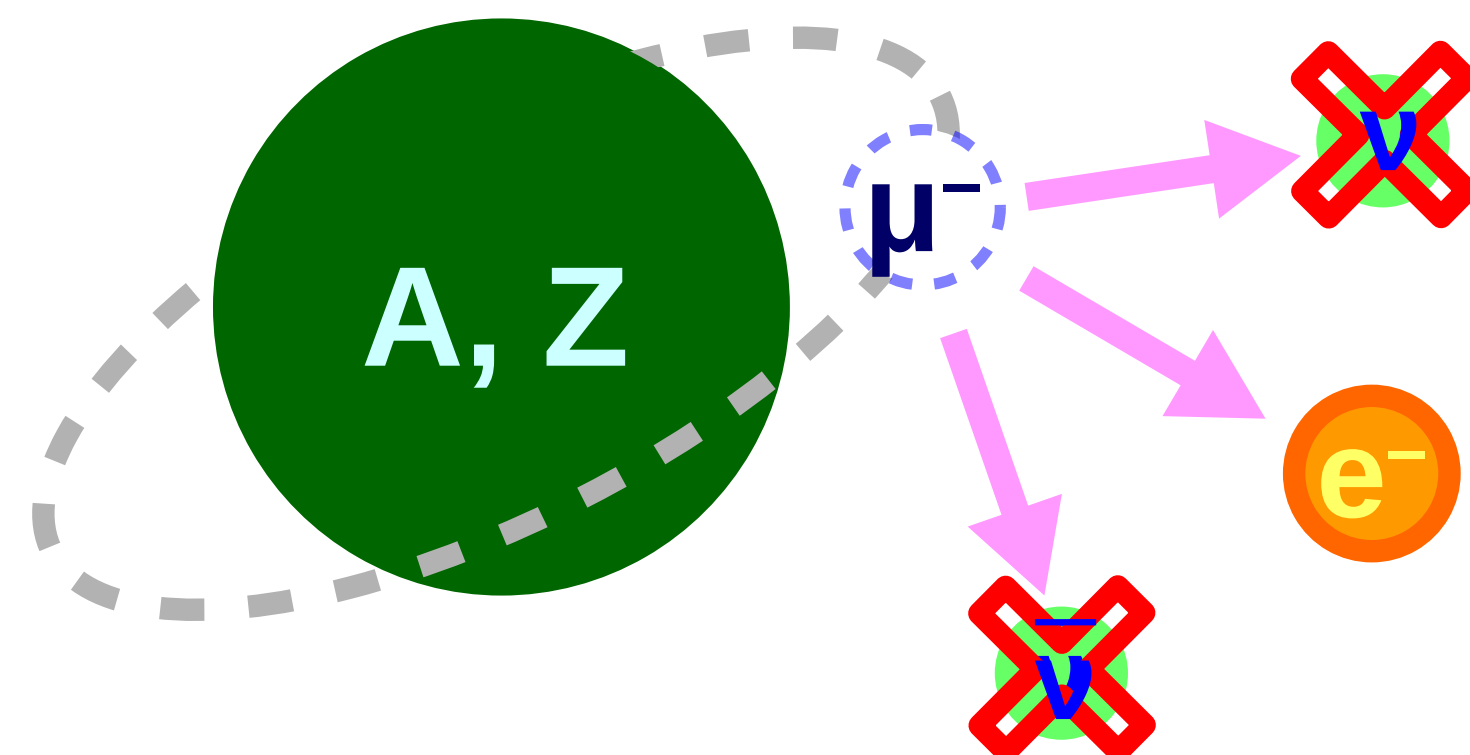
# Needs for SiC sensor: COMET at J-PARC

- COMET (COherent Muon to Electron Transition) starts from 2027 (one of the KEK core projects).
- They require rad-hard beam monitors for high-intensity 8 GeV protons / secondary particles.



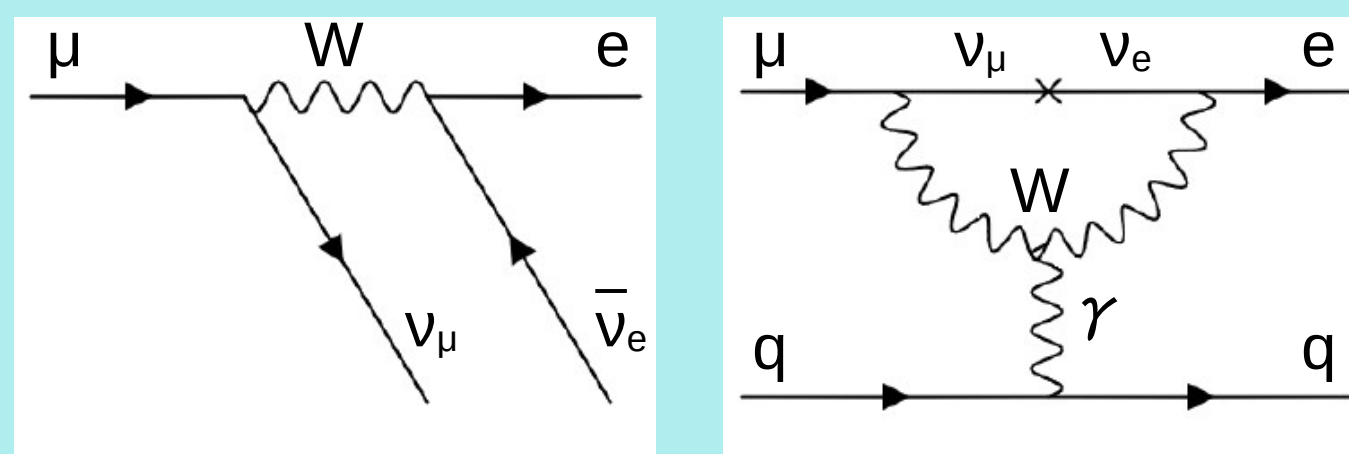


# What do we do in COMET: Muon to Electron Transition



- Conversion of a muon to an electron is “**Charged Lepton Flavor Violation**” process and strongly prohibited in the Standard Model.
- Its discovery is an evidence of the new physics.

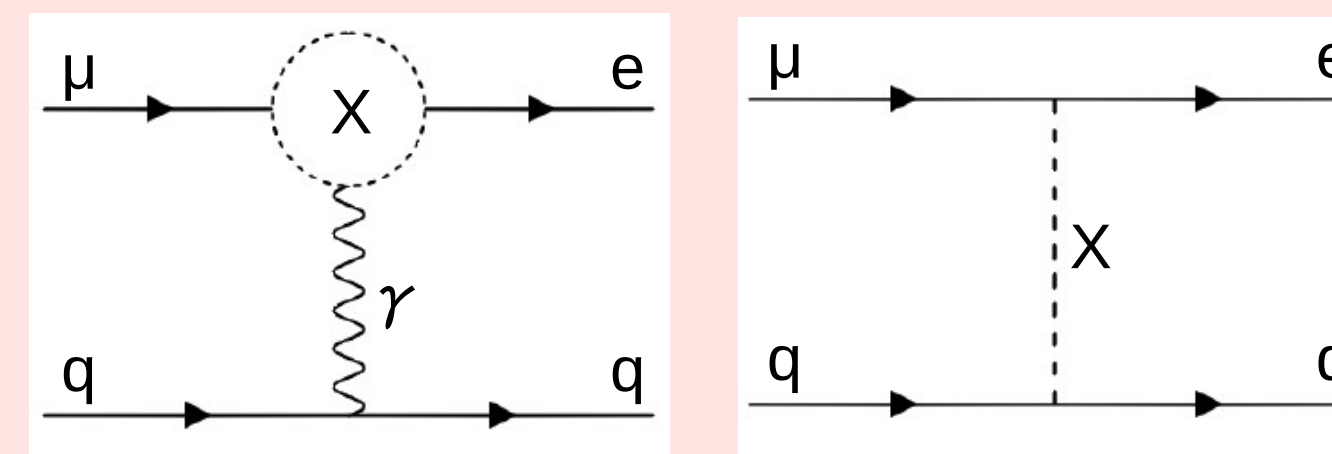
## Standard Model



- ✓ Muon can decay to electron with neutrinos.
- ✓  $\mu$ -e conversion via neutrino oscillation is  $<O(10^{-54})$ .



## New Physics



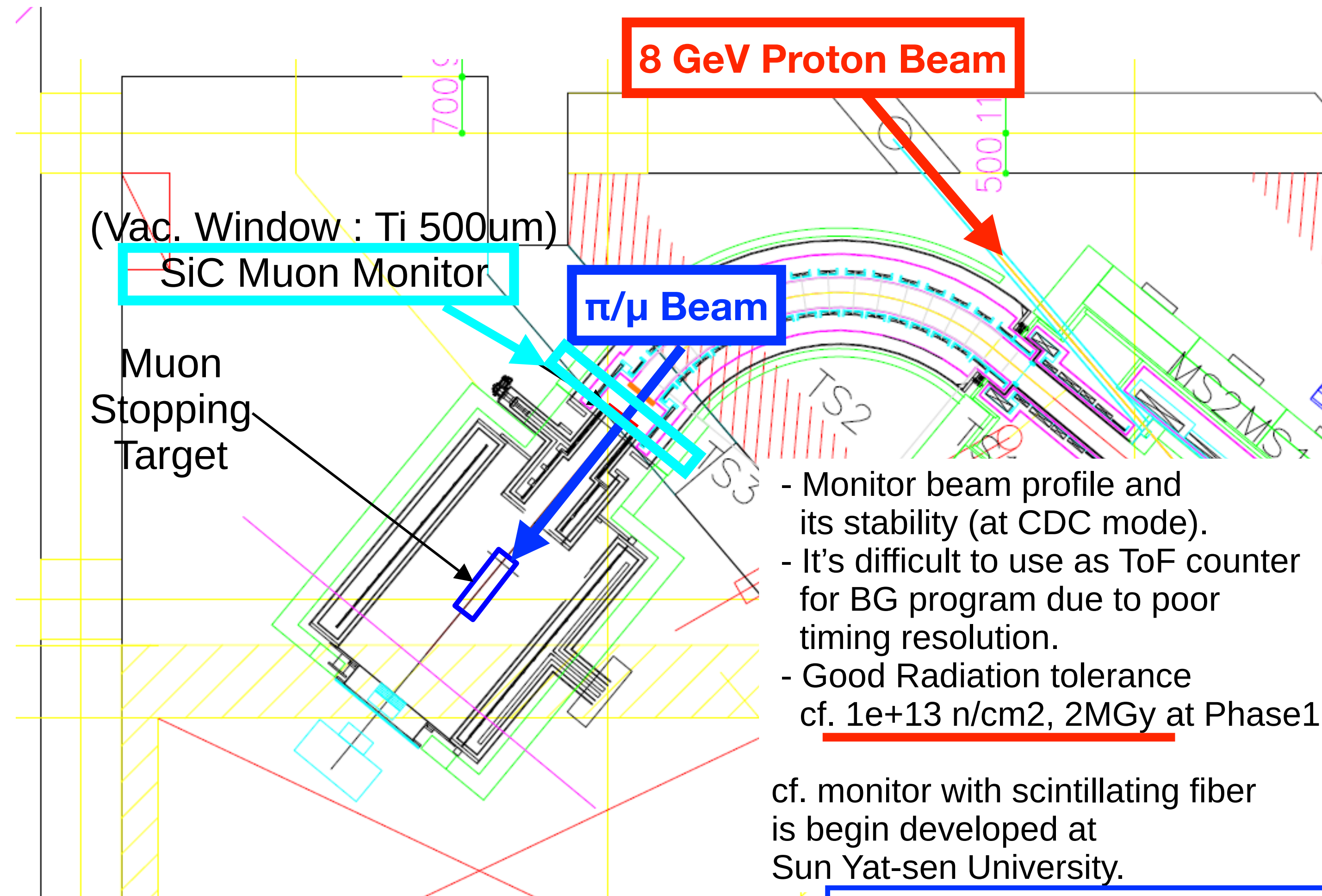
- ✓ Sensitivity for the new physics scale is  $>1000\text{TeV}$ .
- ✓  $\mu$ -e conversion has sensitivity to both photonic and non-photonic interaction.

It's good opportunity to install “own” detectors to contribute to new physics!



# COMET Phase-1

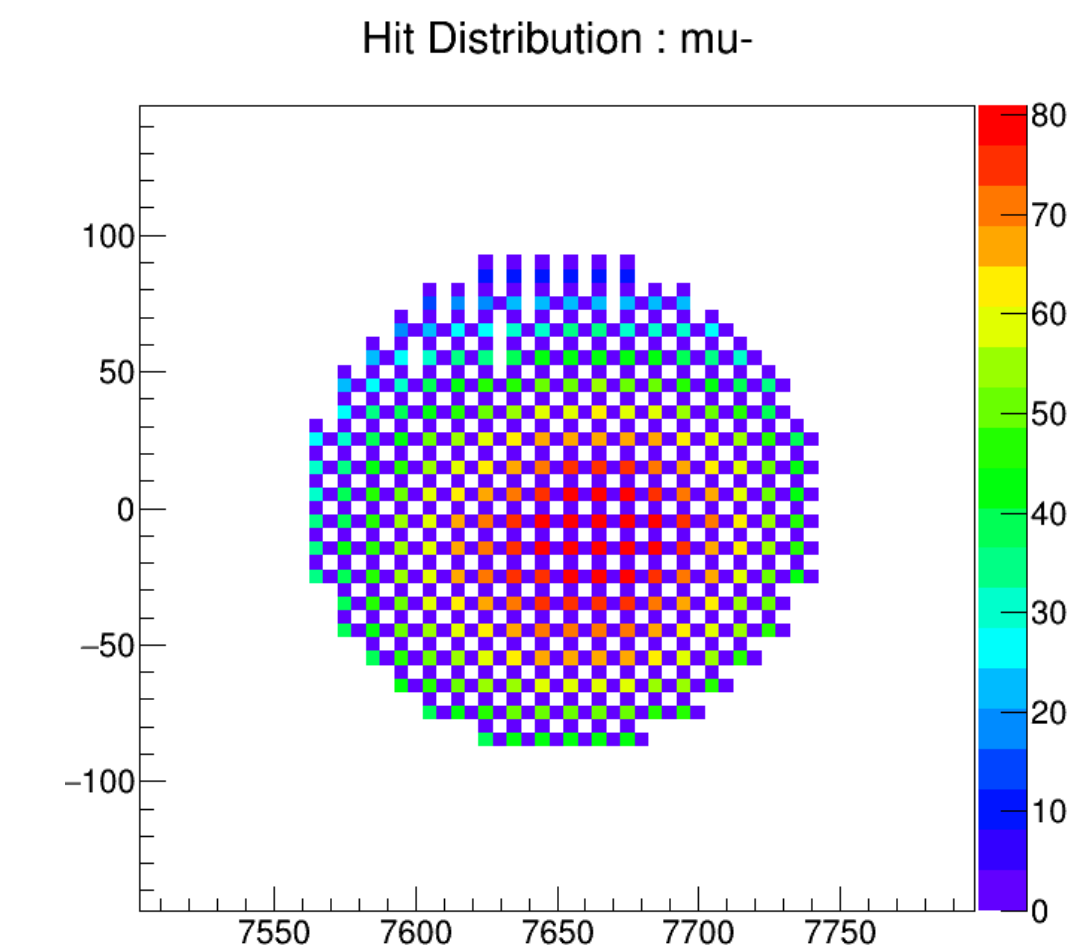
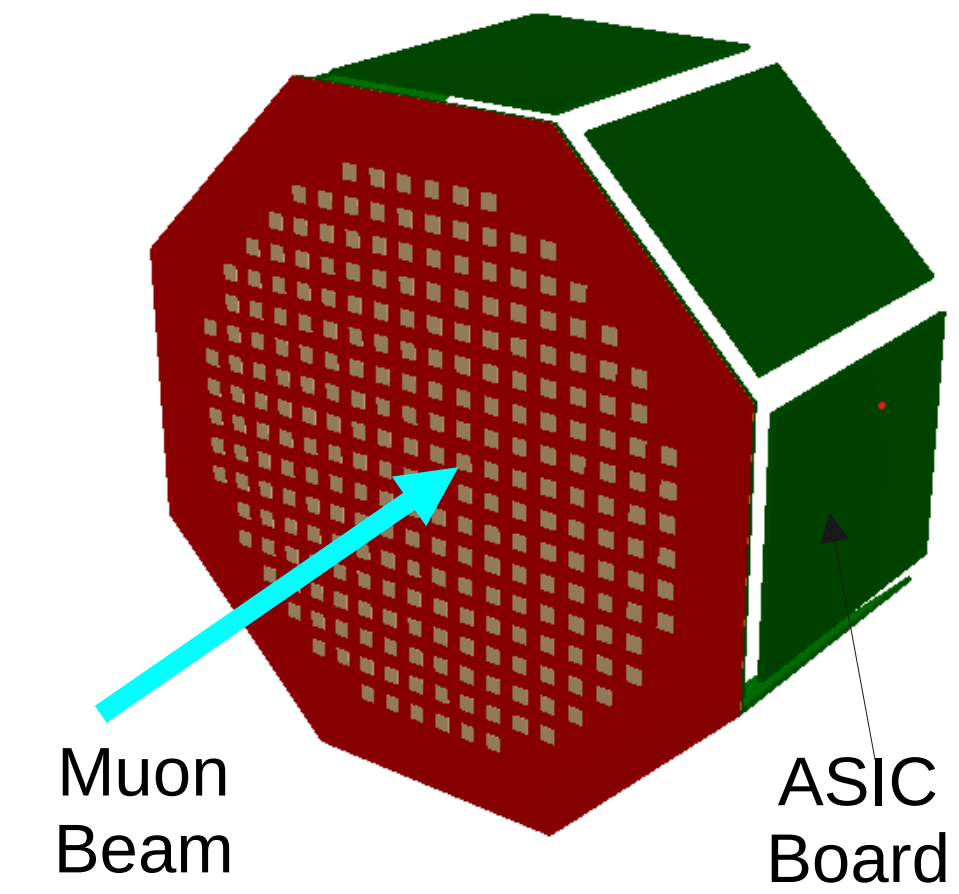
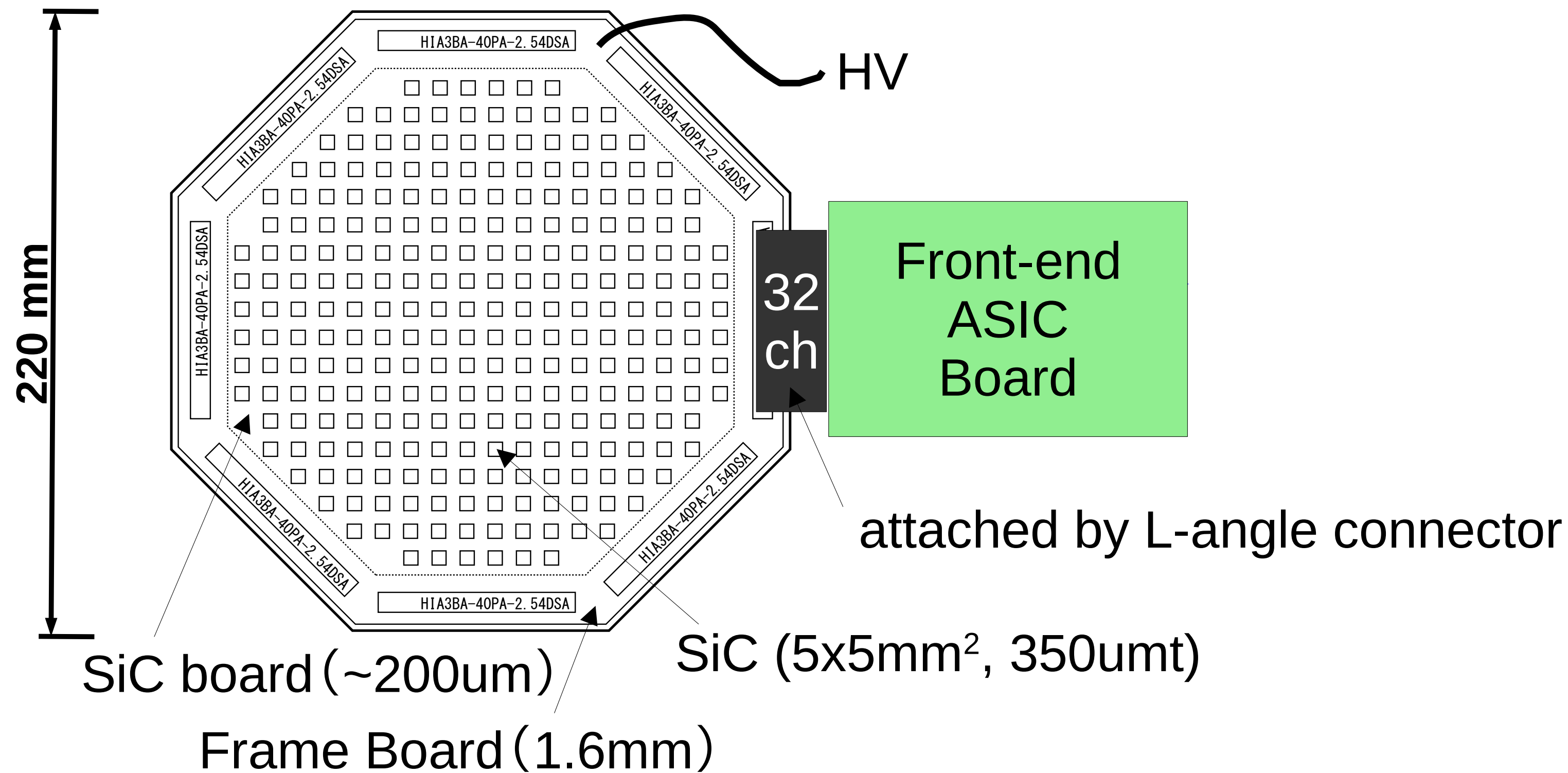
- 8 GeV proton beam is injected to Pion production target.
- Pions decay to muons during transportation in Solenoid magnet.



**Radiation-tolerance is the key to the muon beam monitor.**



# Concept of SiC Muon Beam Monitor



- Center region is thin Kapton board. Edge region is normal board to support the center region.
- Signal wires run between SiC sensors.

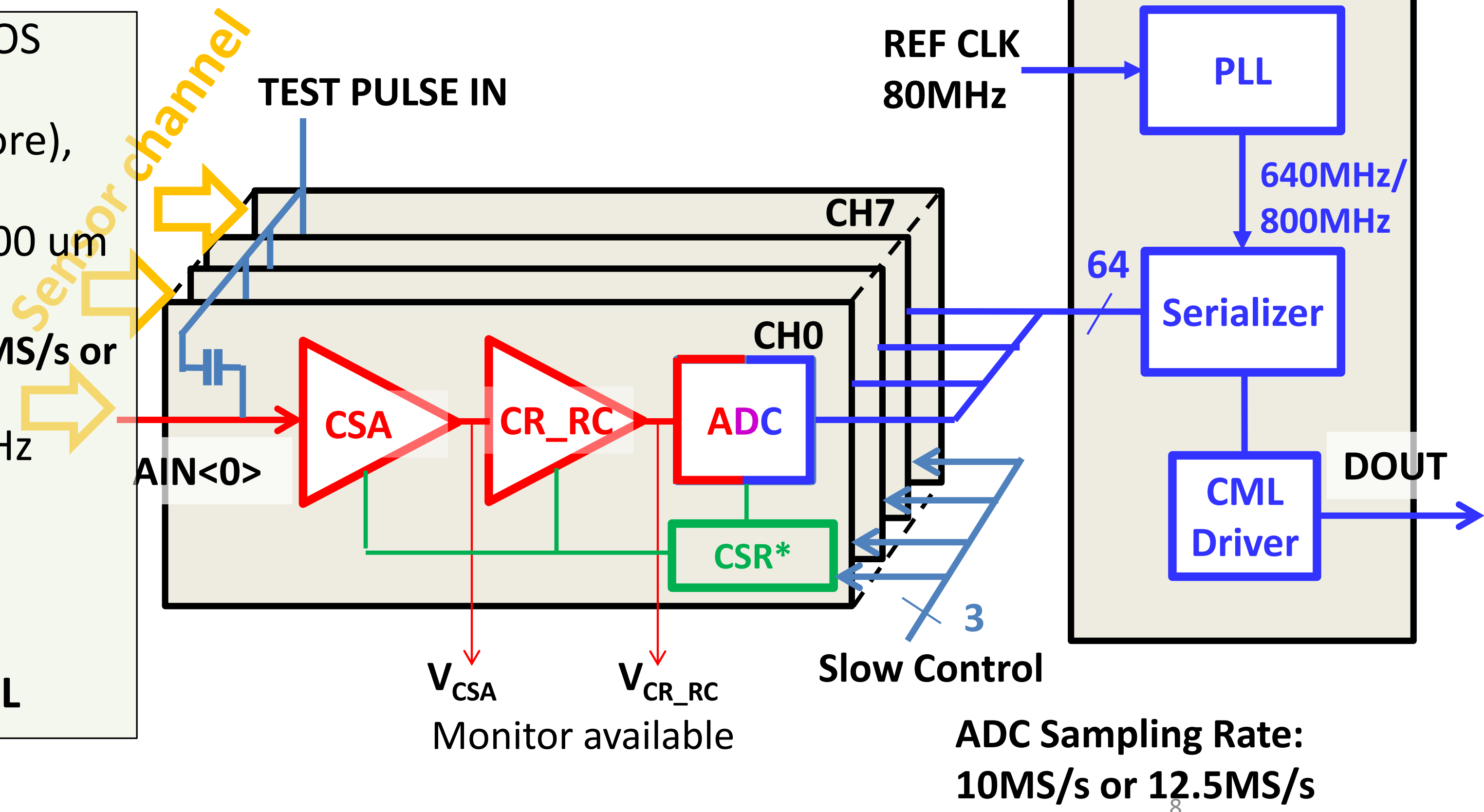
$Q_{sig}$ : 75 MIPs (11 ke-/MIP), continuous waveform digitizing in 10 MHz.



# Readout electronics (SCIBER-1, Silicon Carbide IC for beam monitor)

## • 8ch Amp-Shaper-ADC w/PLL

- Technology: TSMC CMOS 65nm LP
- Supply Power: 1.2V (Core), 1.8V (I/O)
- Chip size: 960um x 2,000 um
- 8-bit SAR ADC
  - Sampling Rate: **12.5MS/s** or **10MS/s**
- PLL: 800MHz or 640MHz (w/80MHz REF CLK)
- Inputs: 8 channels to connect sensors
- Outputs: Digitized differential signals, **CML**

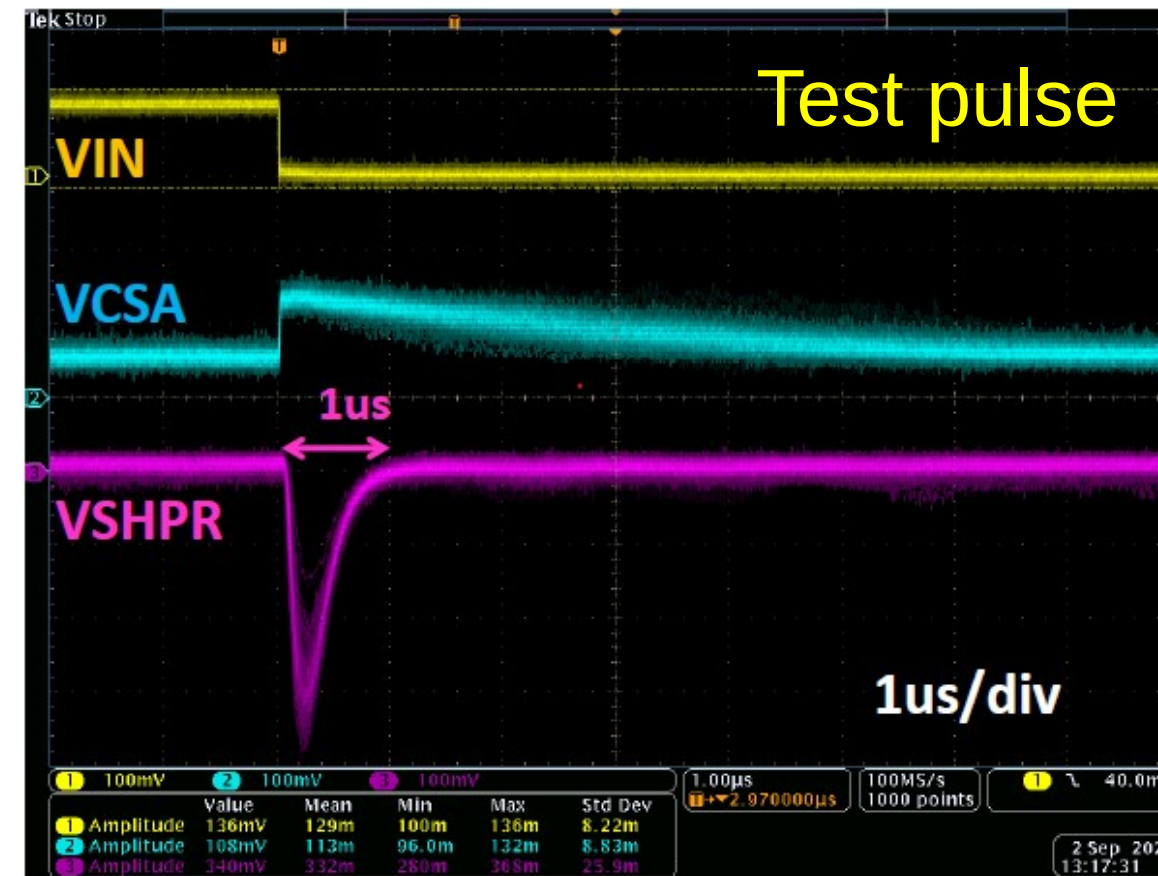
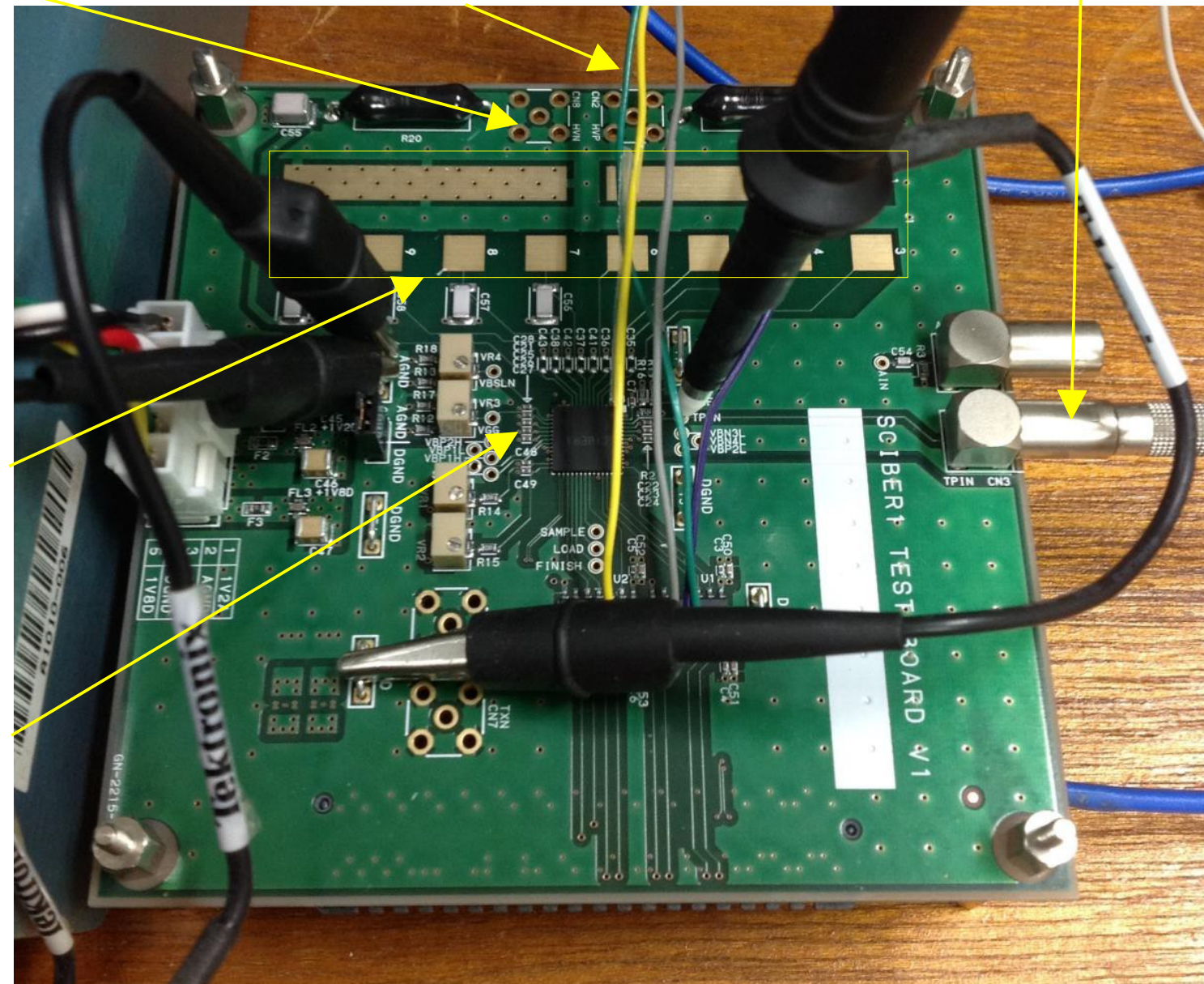


Jakub's talk →

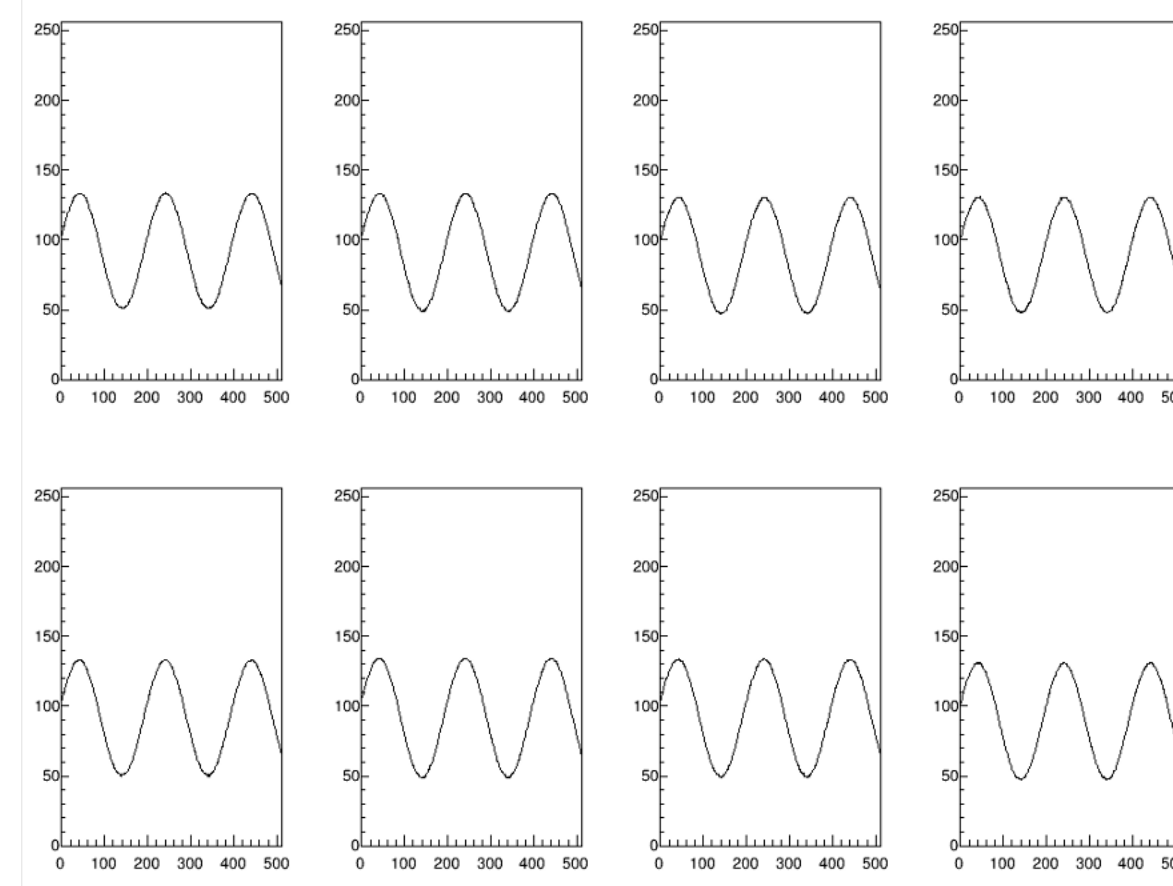


# Preliminary test results

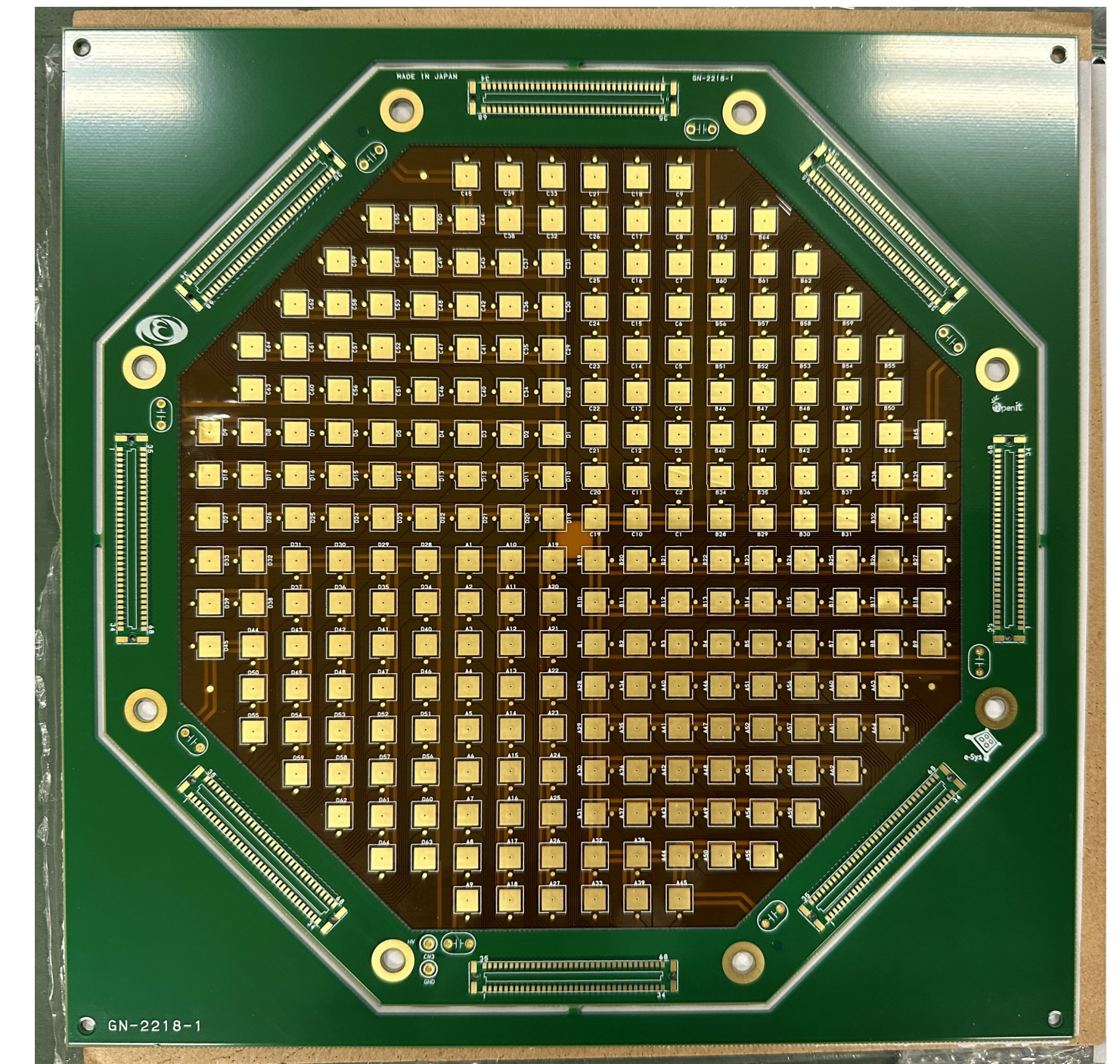
Pad for HV connector      Wires for Slow Control      Pulse Signal



ADC outputs from 50 kHz sin-wave



Prototype of the SiC matrix board



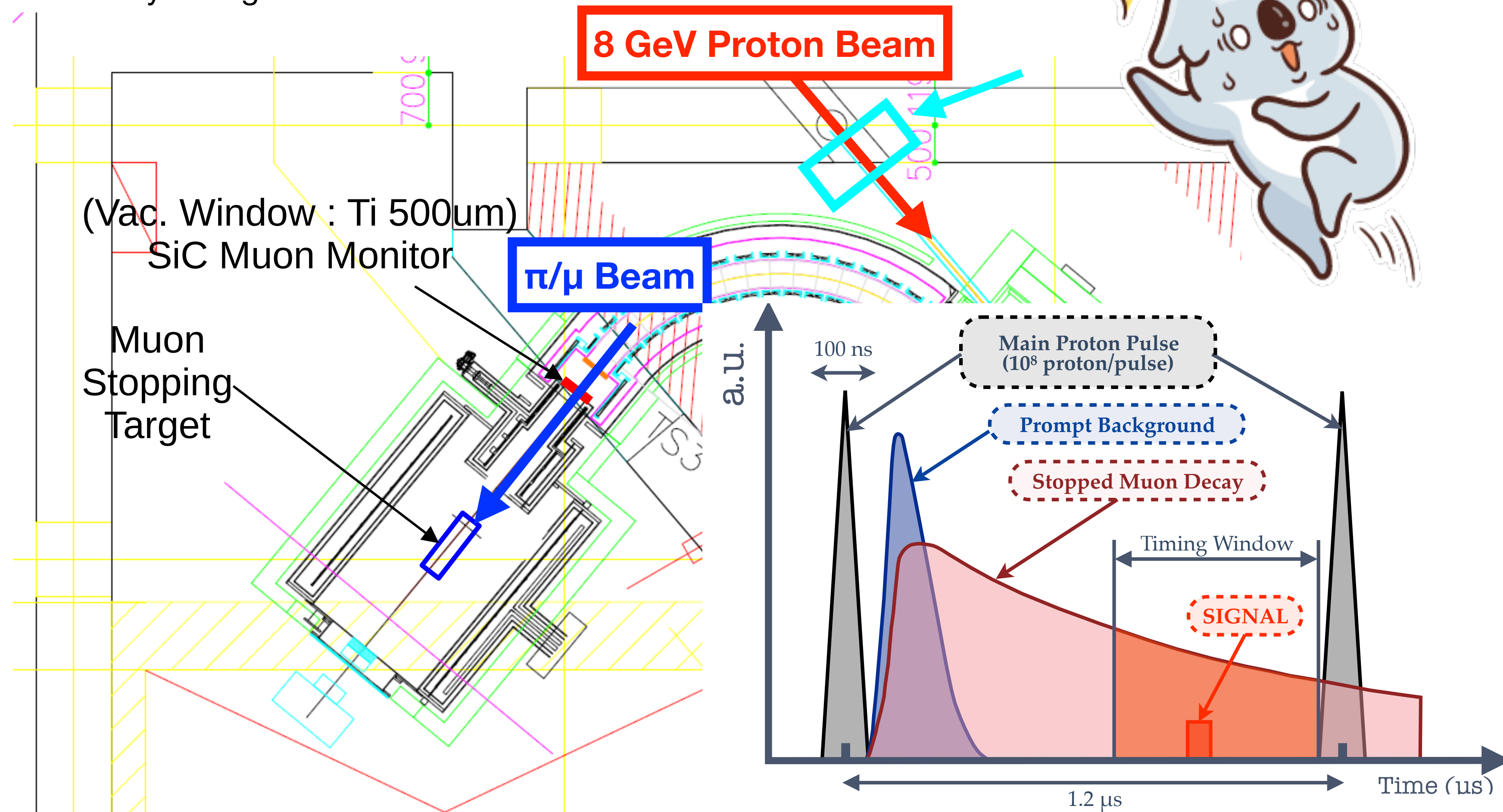
We can make the muon beam monitor on time before the COMET Phase-1.

\*Commercial SiC epi-wafer is another option. (6k euros/wafer).



# Further Needs for SiC sensors (more challenging)

- 8 GeV proton beam is bunched in every 1.2 $\mu$ s.
- Pion is BGD. Select muon events by timing difference.

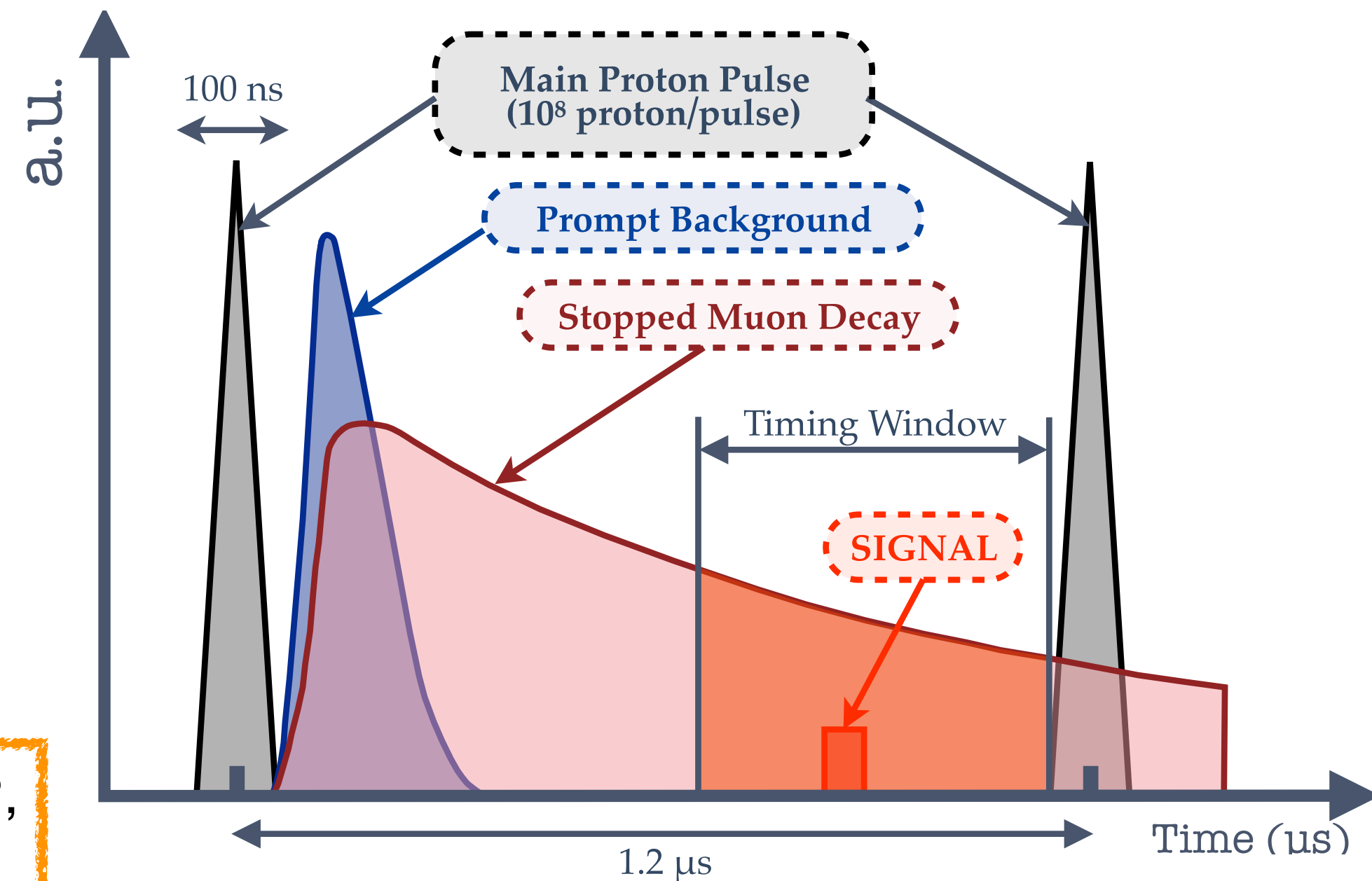


Want to confirm no leaky protons (extinction) between bunches.  $\rightarrow$  On-axis beam monitor with SiC!

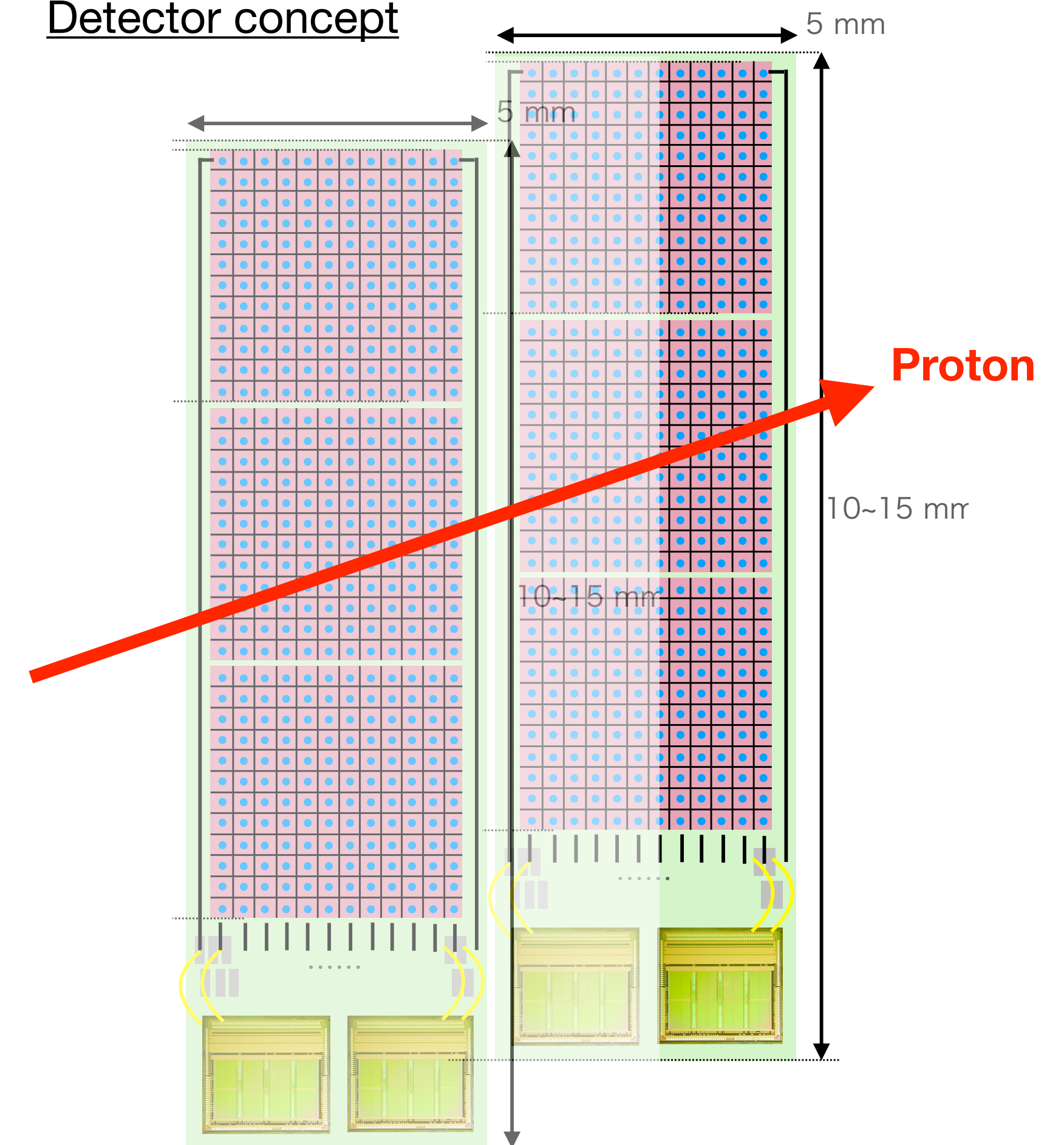


# Requirements for Extinction Monitor

- Want to detect 1 proton after the main bunch
- Max.  $1.6 \times 10^7$  proton/bunch with beam spot of  $\phi \sim 1$  cm (TBD)
- Neutron fluence of  $2.1 \times 10^{14}$  n<sub>eq</sub>/cm<sup>2</sup> during Phase-1



Detector concept



Why SiC?,  
realistic?

1. Relatively **large-area devices** can be fabricated in **wafer process**. → many detectors
  2. Machine maintenance period is available every week. → We replace the detector!
- **Electrodes should be segmented (pixel/strips) to reduce the event rates.**
  - Readout electronics placed sideways to avoid proton beam spot for radiation reason.

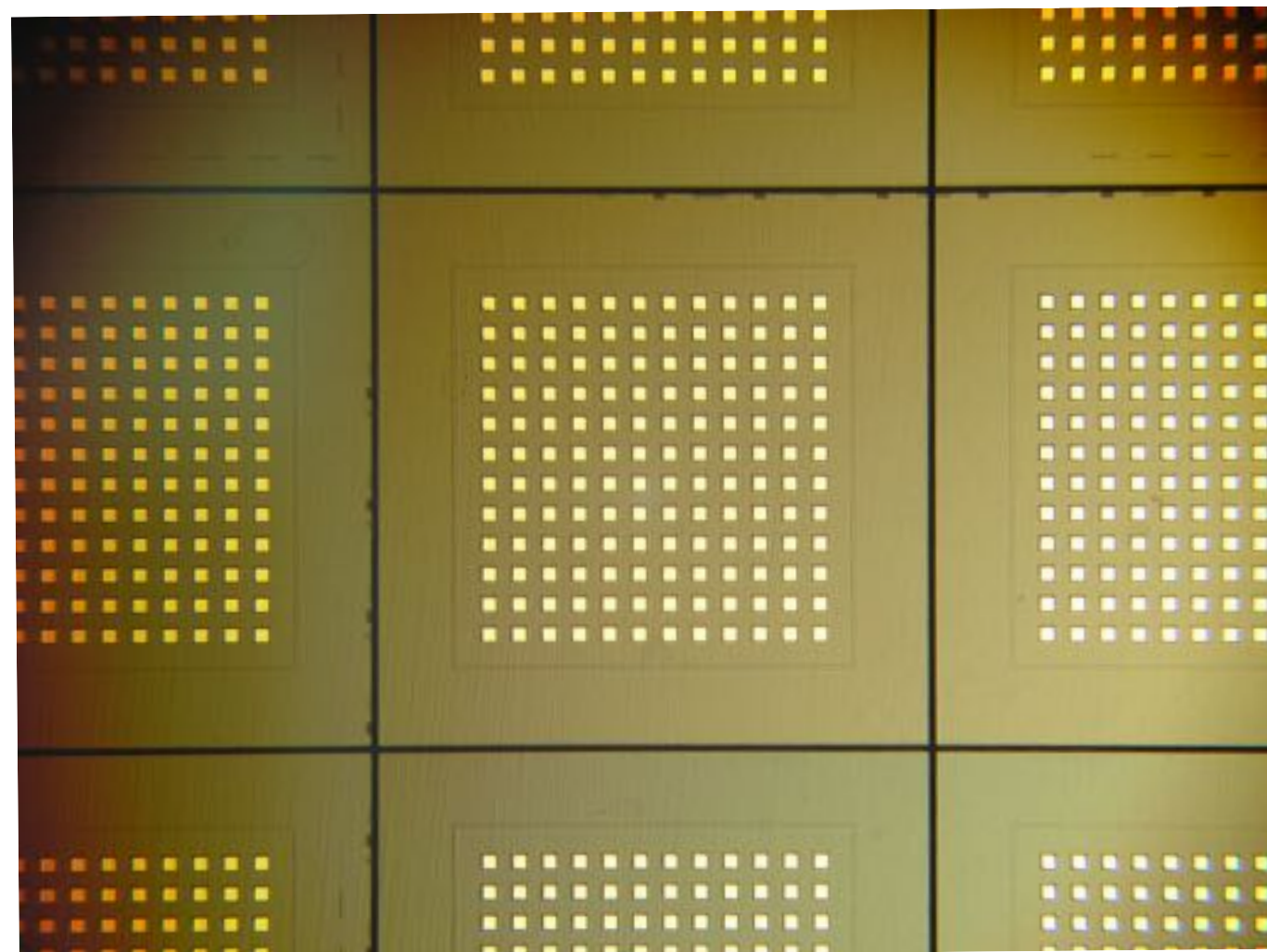
To prove the concept, we investigated the **sensor segmentation** and performance uniformity.



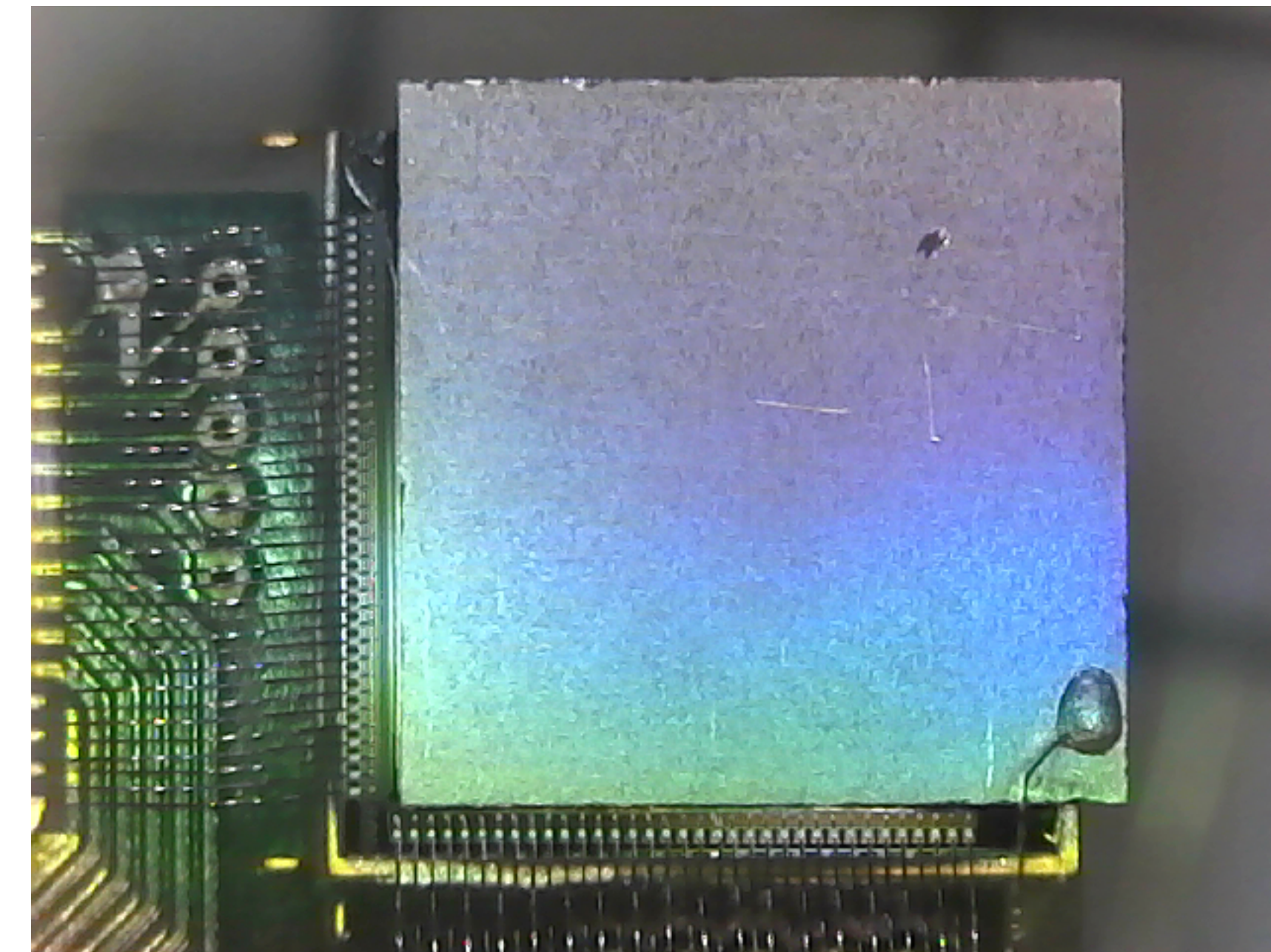
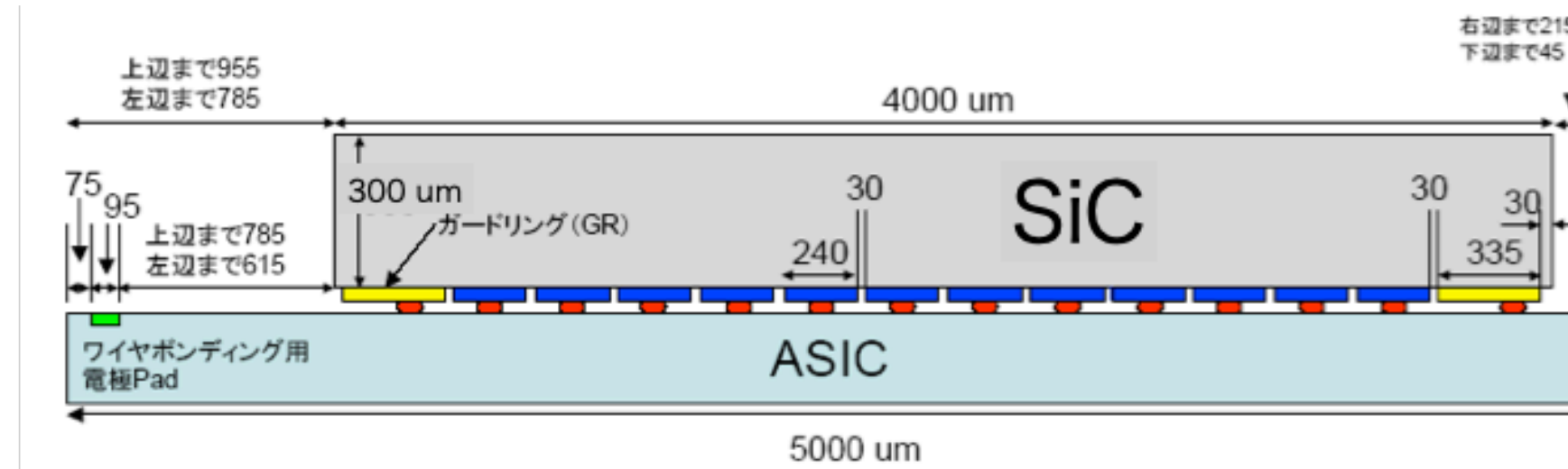
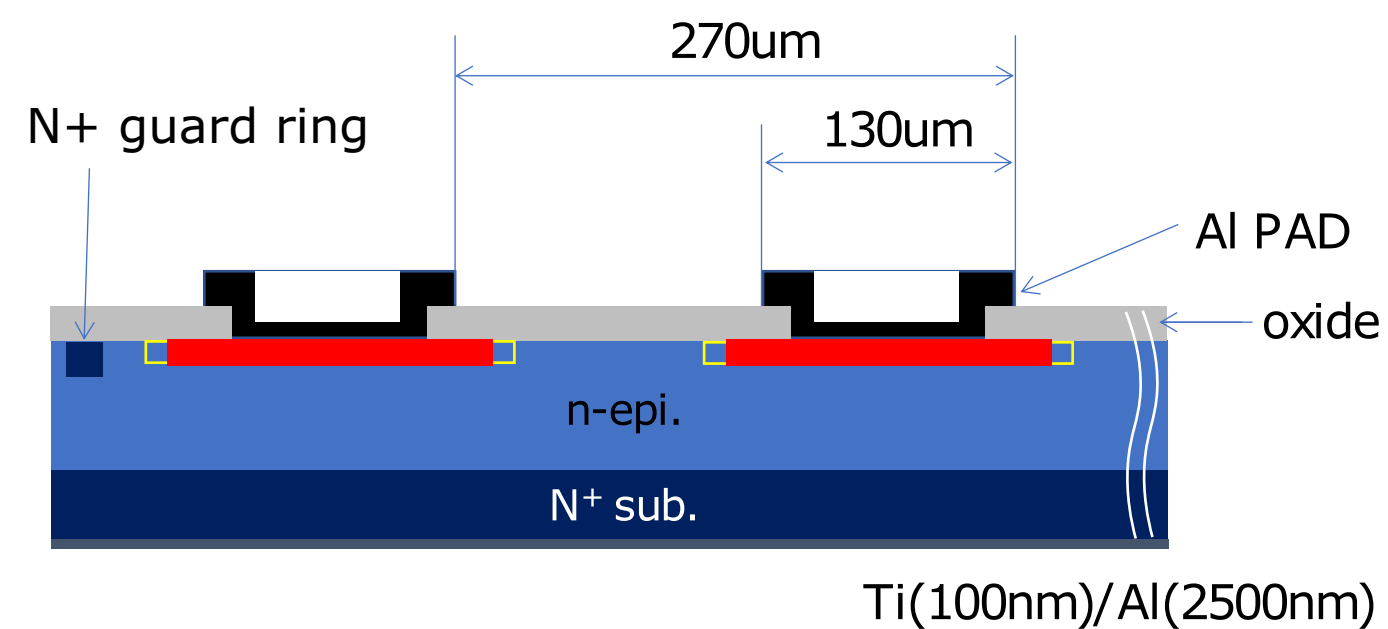
# Sensor segmentation (hybrid pixel detector)

- 5 mm x 5 mm with 12 x 12 electrodes, 270  $\mu\text{m}$  pitch
- readout with low-noise ASIC
- Au/In stud bump technology

(a)



(b)

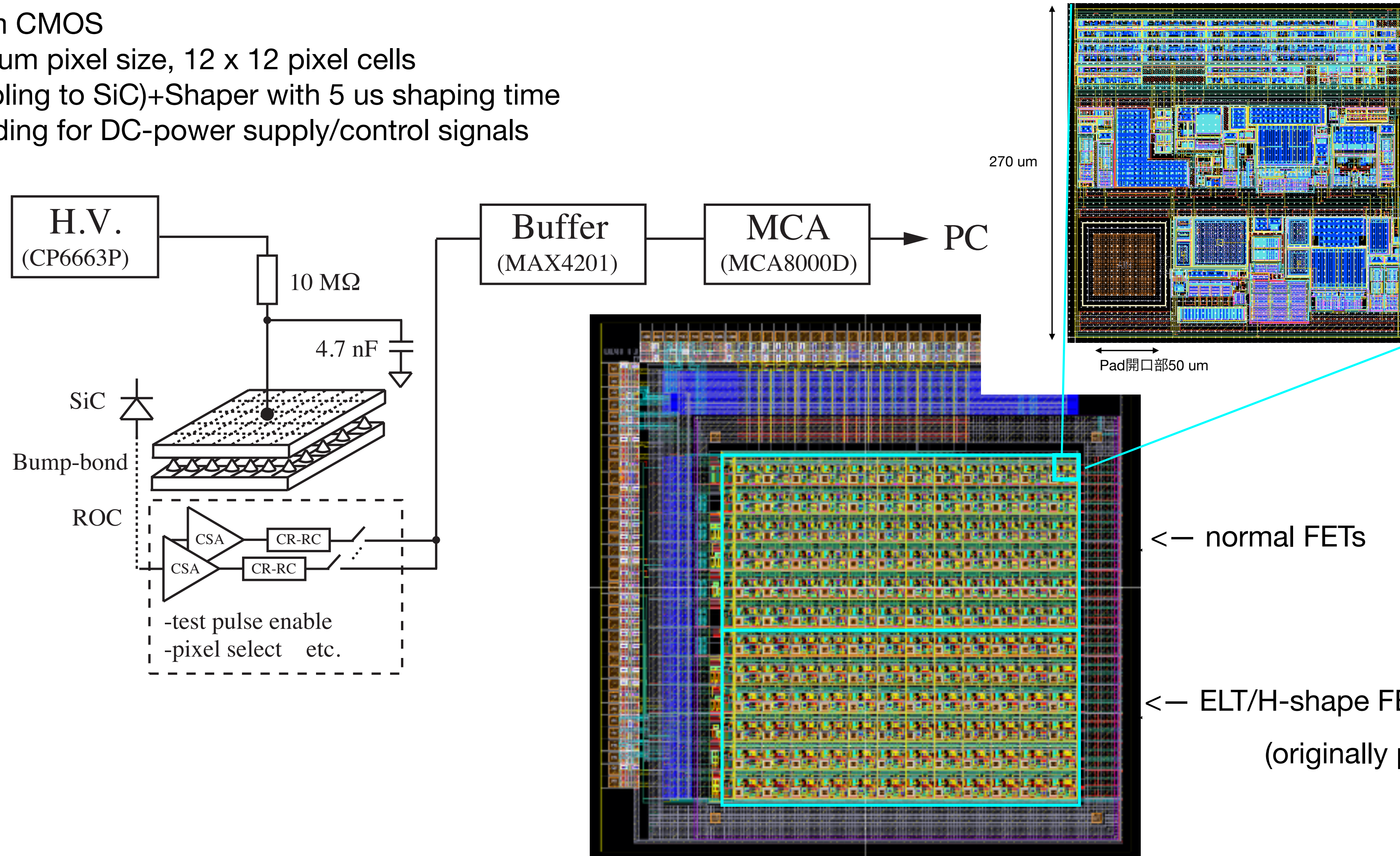


Passivation (Parylen or Silicone rubber) is necessary to prevent electric discharges @1 kV.



# Readout ASIC

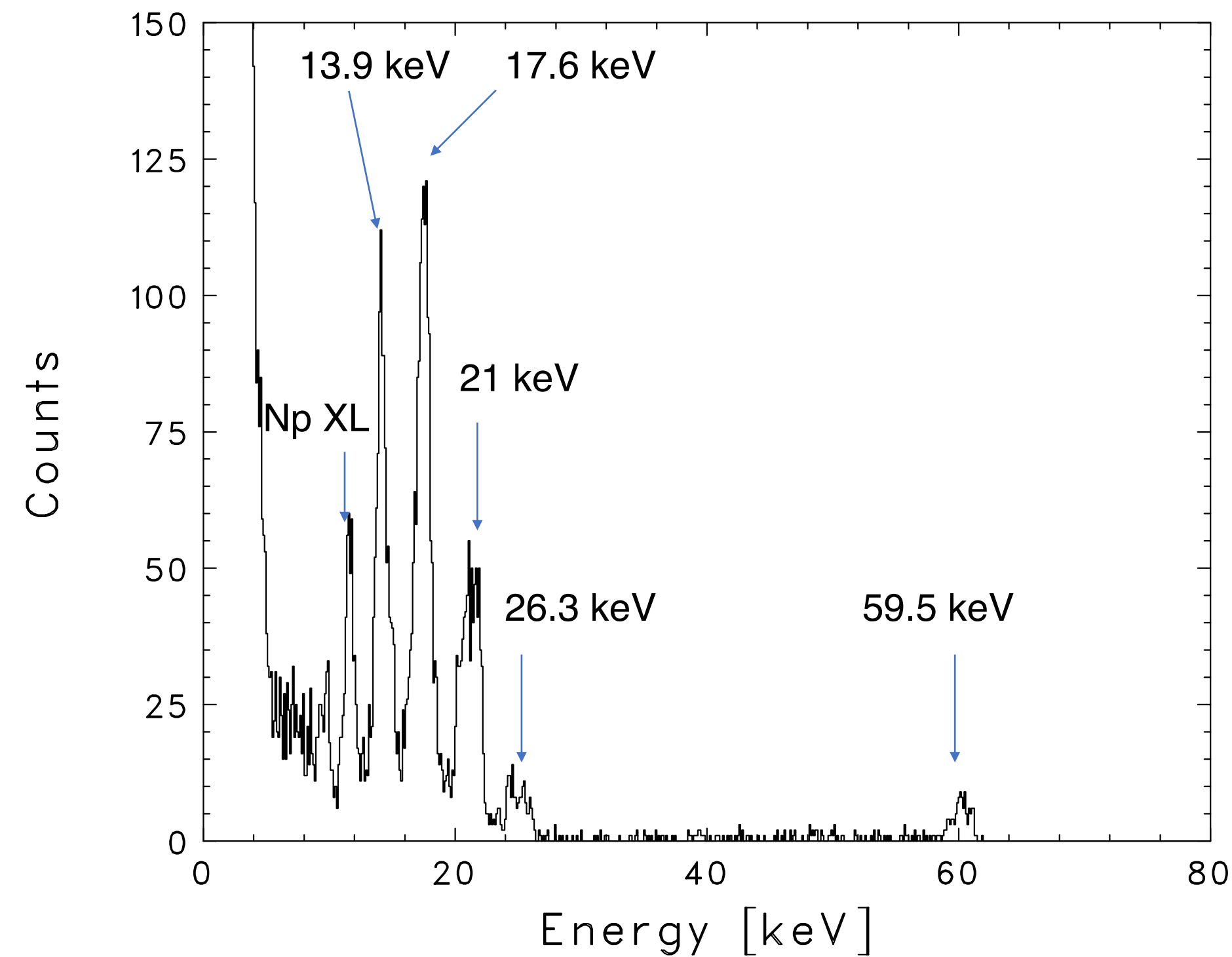
- TSMC 0.35  $\mu\text{m}$  CMOS
- 270  $\mu\text{m}$  x 270  $\mu\text{m}$  pixel size, 12 x 12 pixel cells
- CSA (DC-coupling to SiC)+Shaper with 5  $\mu\text{s}$  shaping time
- Used wirebonding for DC-power supply/control signals





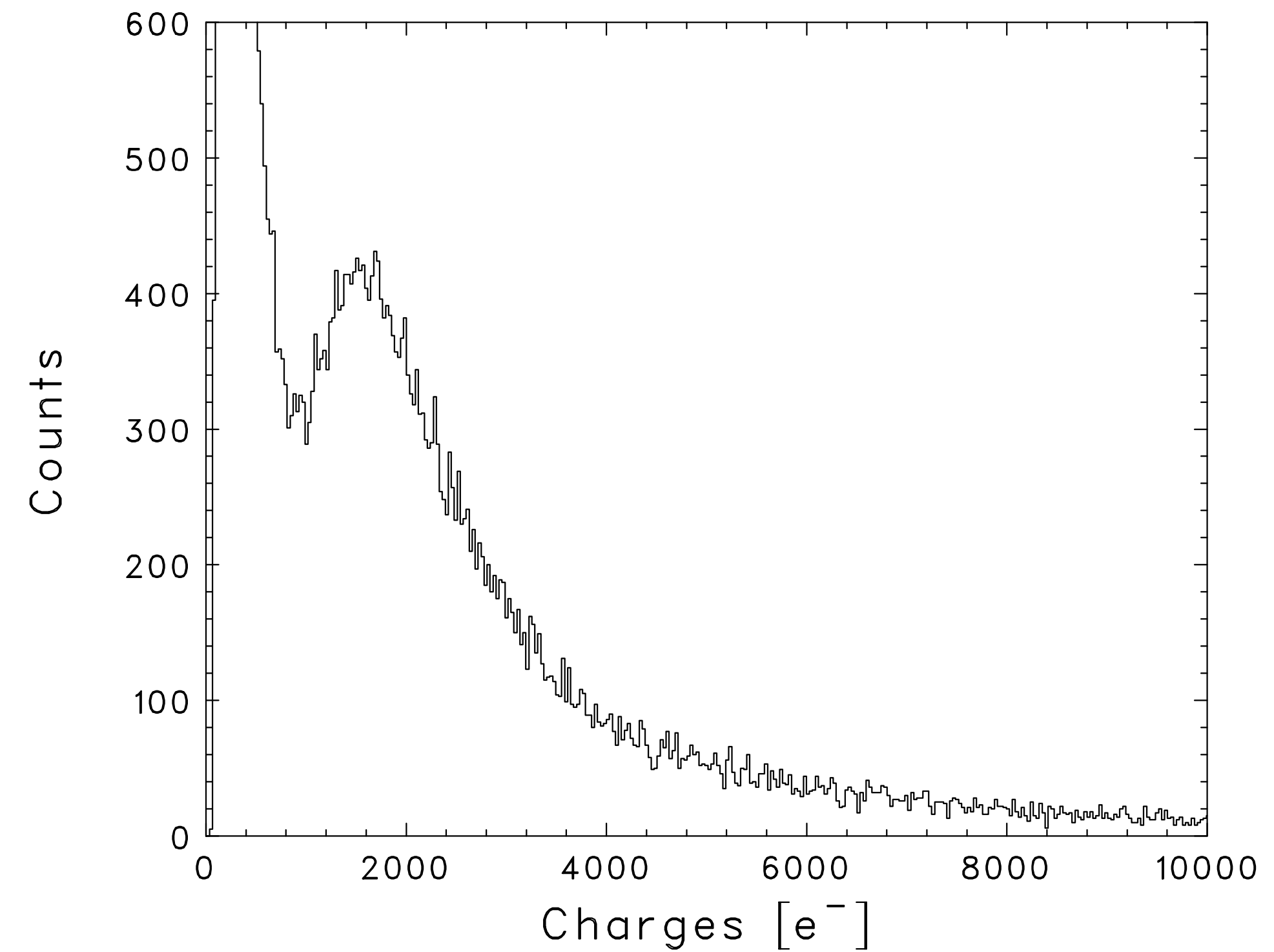
# Spectral performance

- HV: +600 V
- Exposure: 3 days
- Mode: HG



FWHM: 1.72 keV @17.6 keV

- HV: +600 V
- Exposure: 0.5 days
- Mode: HG

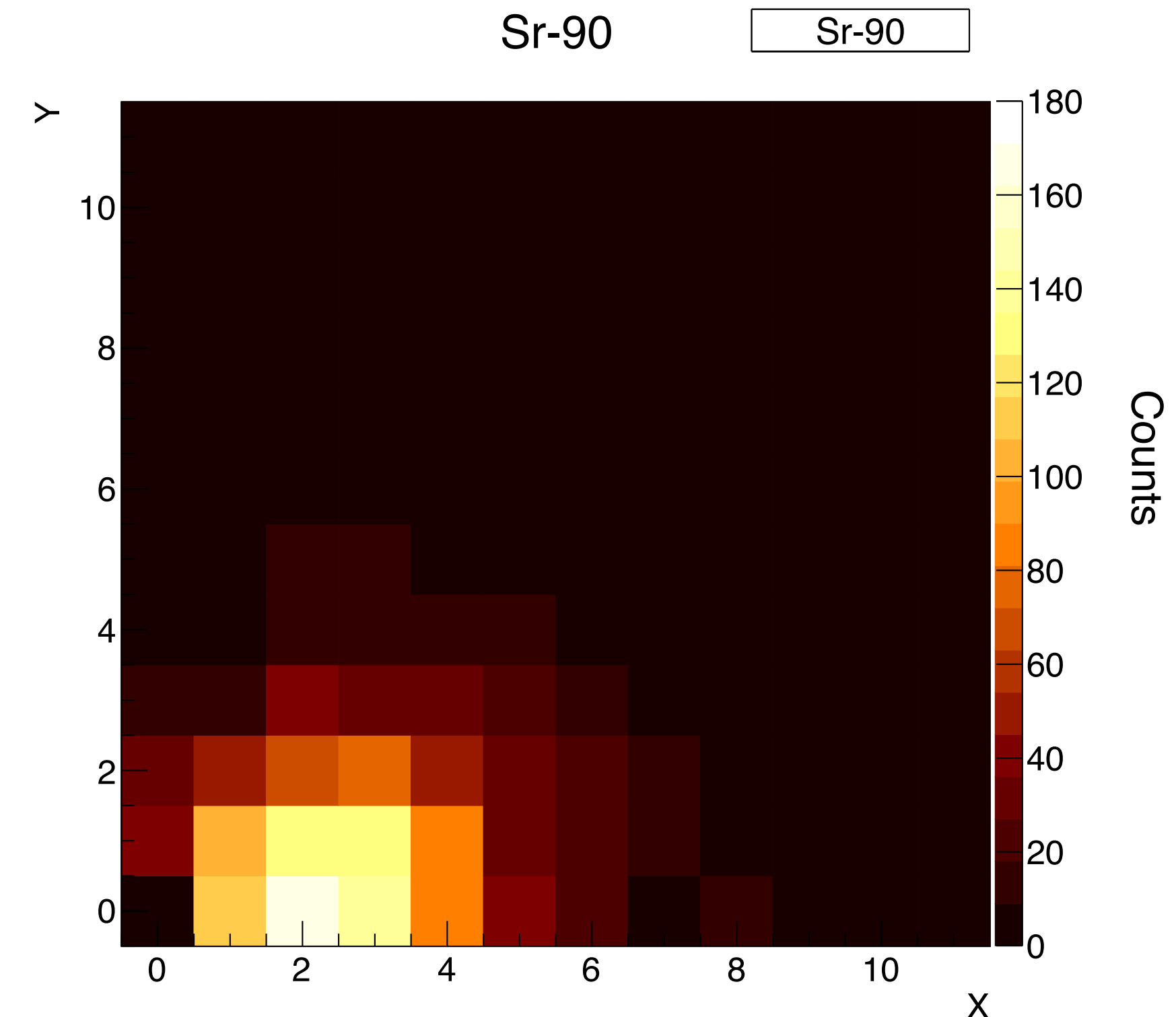
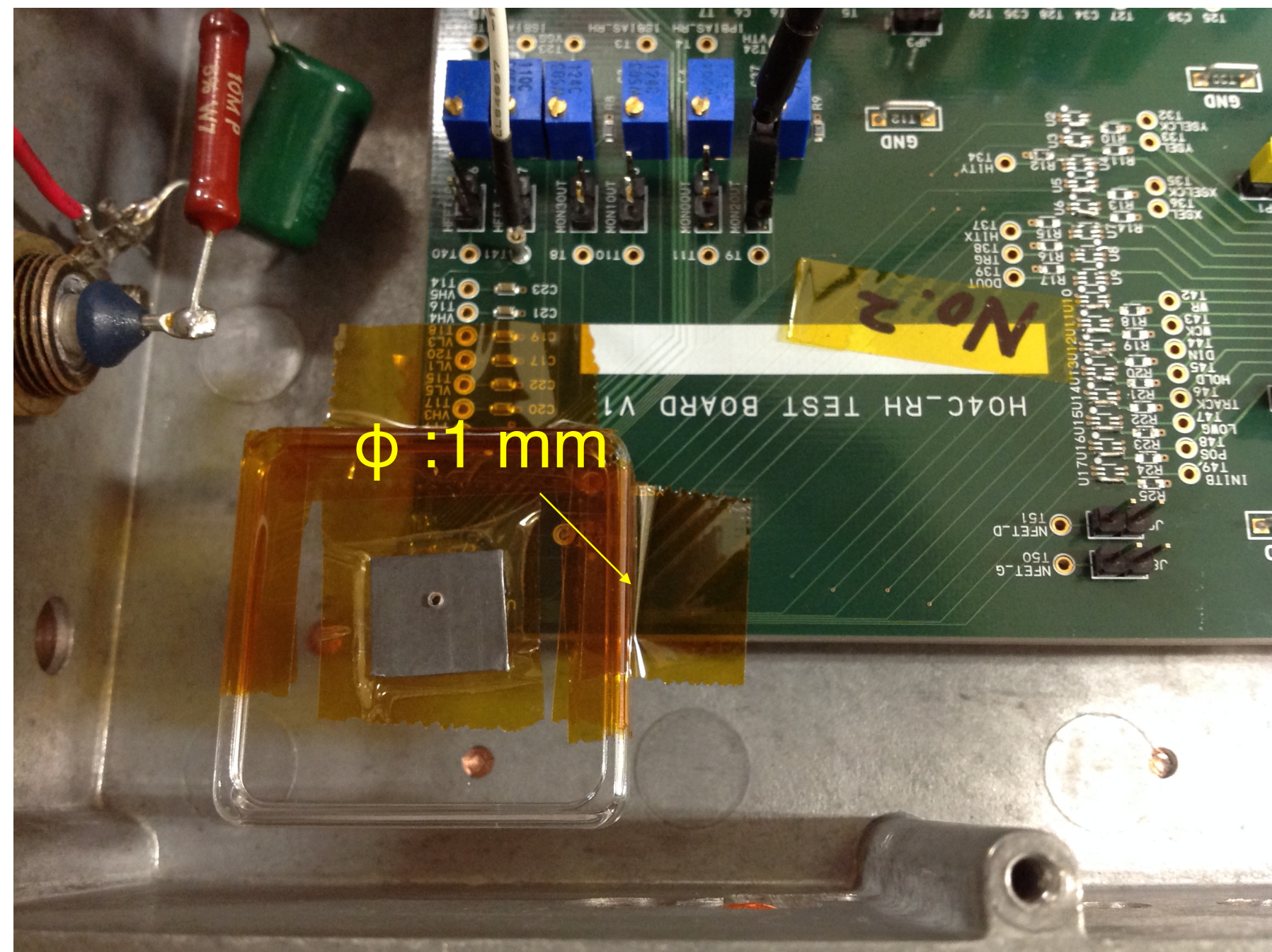


Confirmed  $\beta$ -ray events from all pixels.



# Imaging performance

- Blind search of pinhole position in Pb sheet
- Count Sr-90 events between 1000-6000 e-, 1 min for each pixel



- Finer segmentation is realistic and nice uniformity expectable in larger devices
- SiC performance is closing to silicon.
- Still long way to reach the proton extinction monitor, but SiC is an important candidate.



# Needs of Diamond sensors

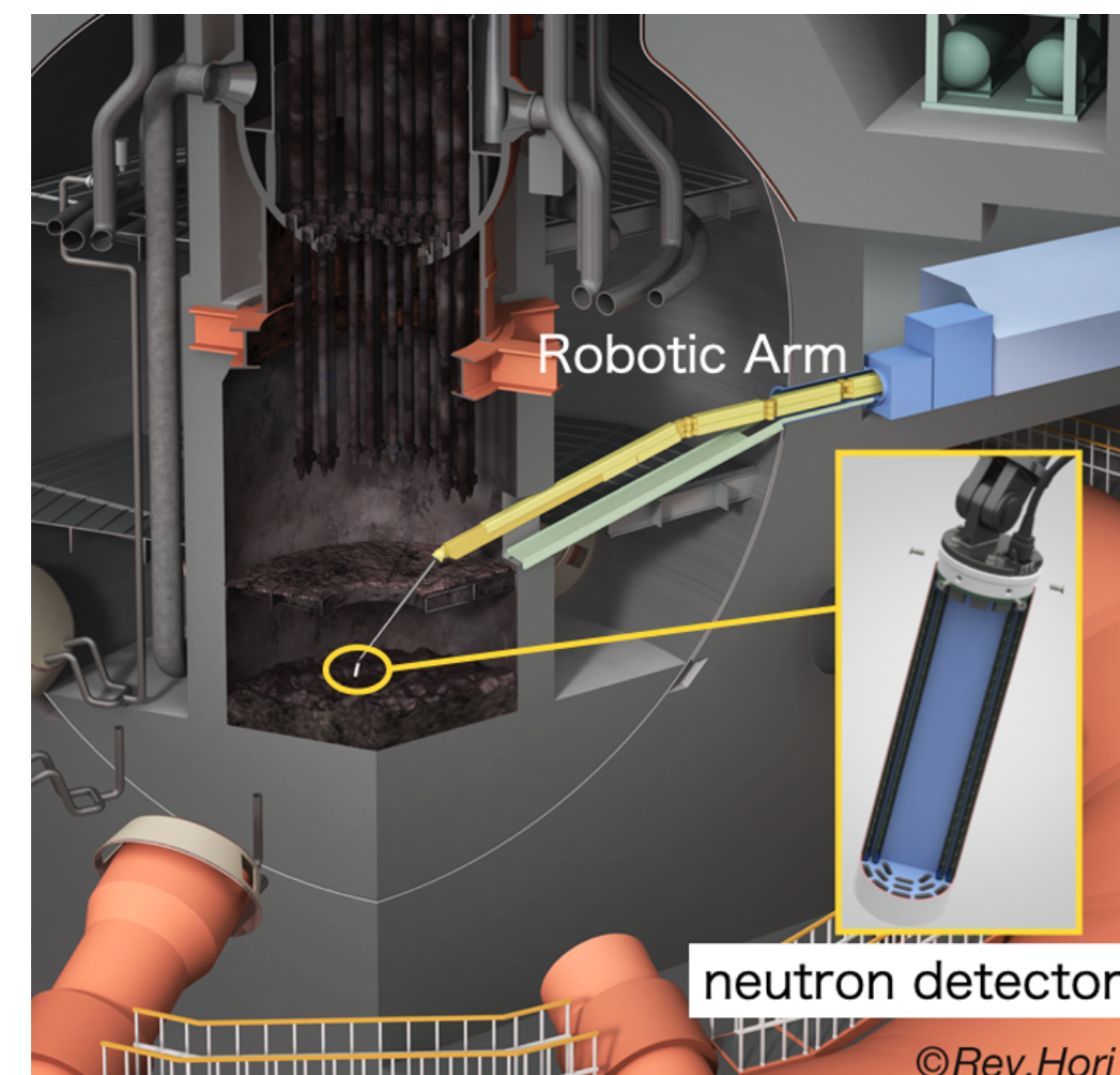
- Nuclear decommission is on-going at Fukushima Nuclear Power Plant.
- Need “eye” to know exact locations of nuclear debris for robotic arms (at least monitor the neutron flux to protect workers).
- No data of radiation environment yet.

Gamma-rays from Cs every direction: max. 1 kGy/h (100 krad/h)

Site of the Fukushima Nuclear Power Plant



Concept of the neutron detector



Under high  $\gamma$ -BGD, thin sensors are required for neutron detection. → Diamond!

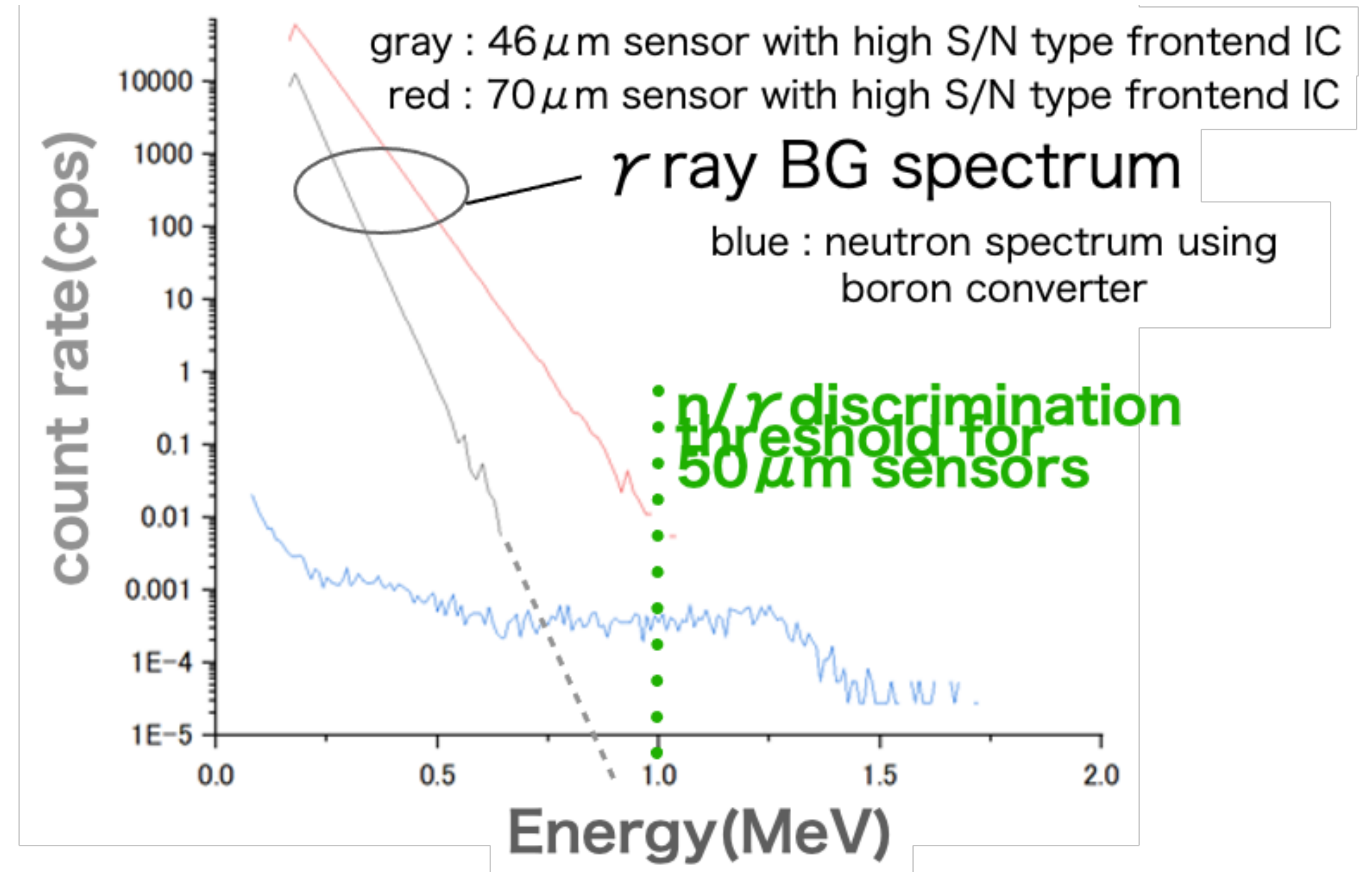
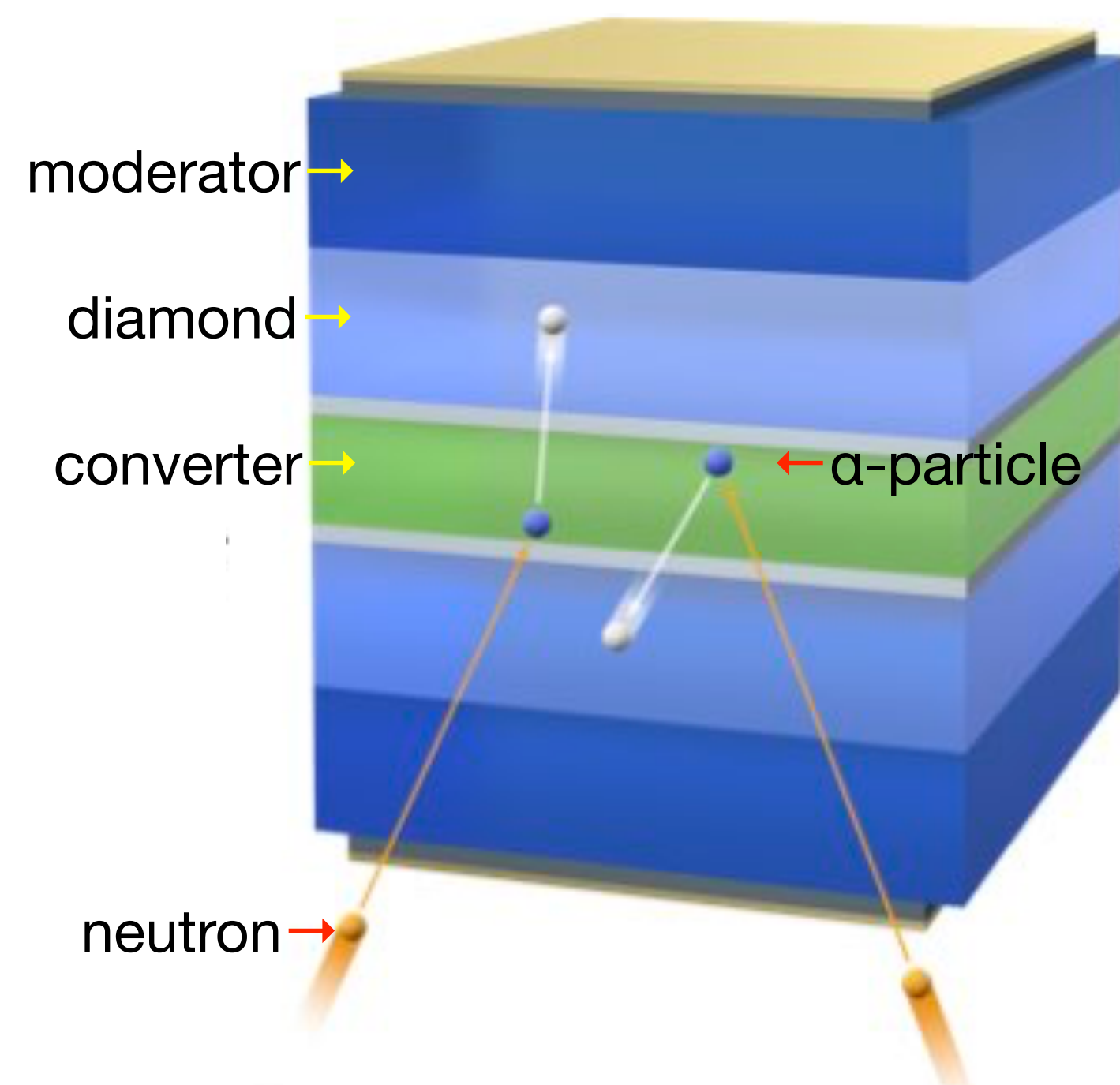
Pacific ocean



# Concept of neutron detector

- Use neutron converters ( ${}^6\text{LiF}/{}^{10}\text{B}_4\text{C}$ ) and detect alpha-particles
- Detect neutrons ( $\sim 1$  Hz) under high gamma-ray BGD ( $\sim 1$  MHz)
- Sandwich configuration to increase detection efficiency

Concept of the neutron detector



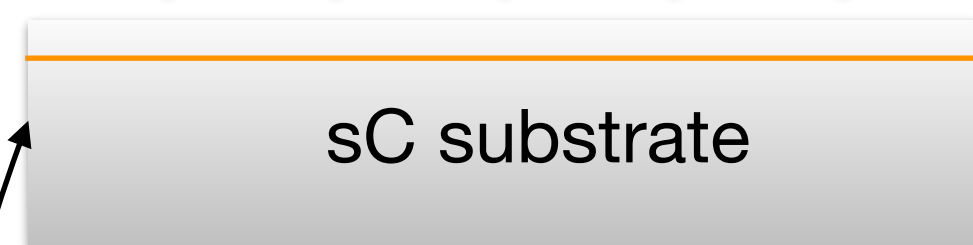
To detect neutrons with 1 Hz, we need more than 1000 diamonds! How to realize such number?



# Device fabrication: self-supported diamond

- Self-supported diamond with **reusable substrate**
- 30-50  $\mu\text{m}$  thickness to avoid cracking
- Na-Nd:  $10^{11}$ - $10^{12}$   $\text{cm}^{-3}$
- Long process time (>2 weeks), yield issues, wire-boning etc.

Carbon ion bombardment 3 MeV,  
 $2 \times 10^{16}$  ions/ $\text{cm}^2$



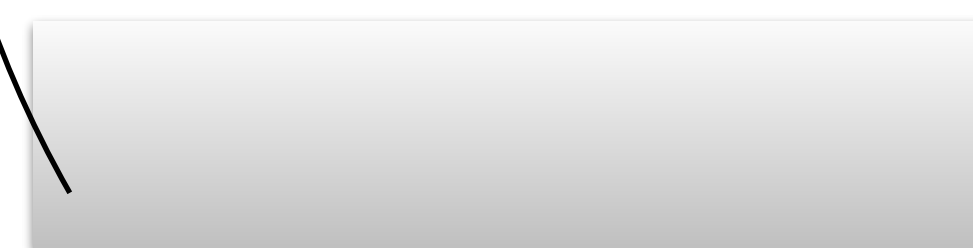
sC substrate

(HPHT IIa)



Self-supported device

Ion beam etching (surface  $\sim 10\mu\text{m}$ )  
+ implant p+ layer

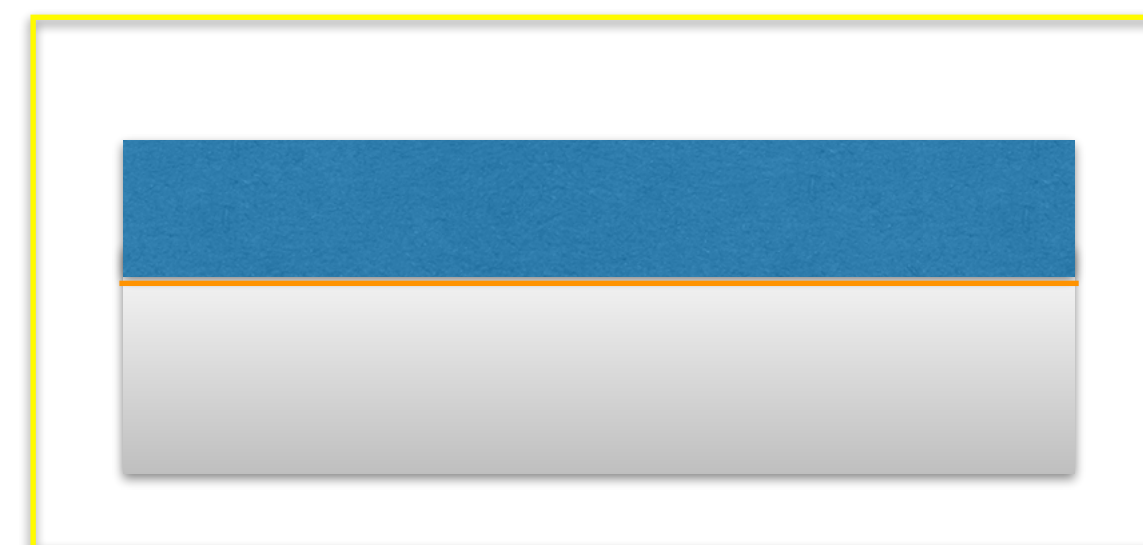


Reusable substrate

CH<sub>4</sub>/H<sub>2</sub> plasma

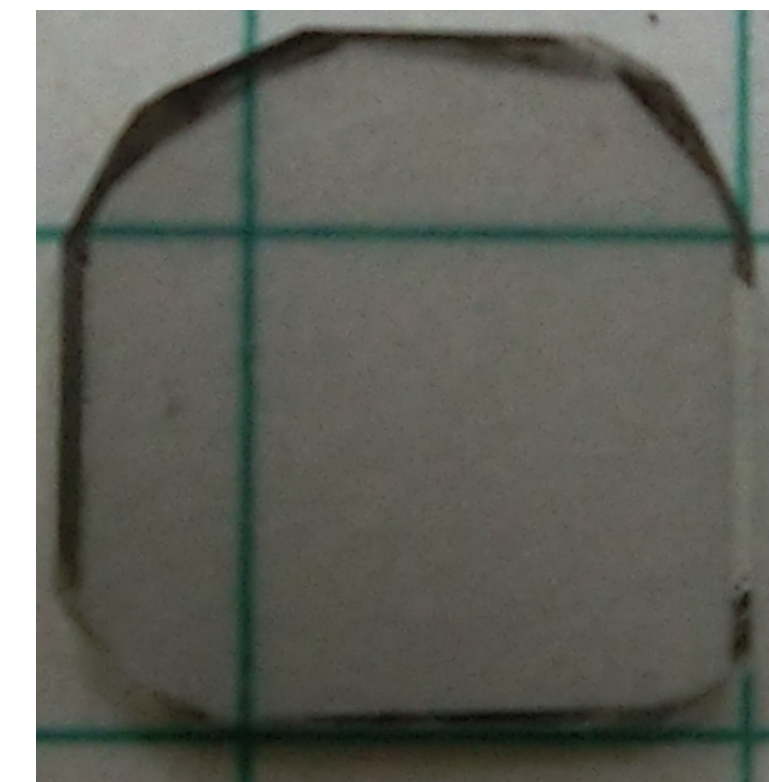
growth layer

Chemical Vapor Deposition

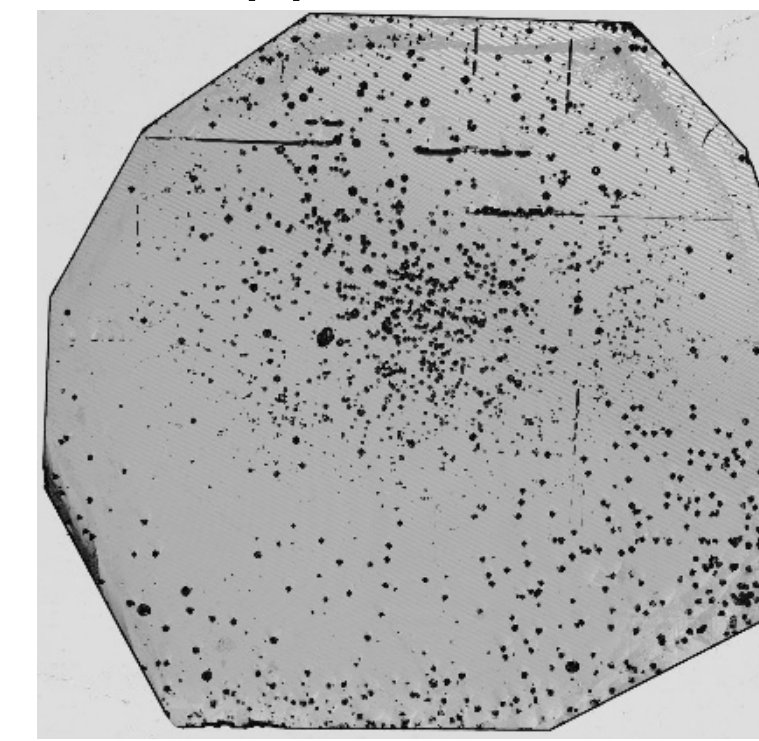


Electrolytic etching

Single-crystal substrate



Self-supported diamond

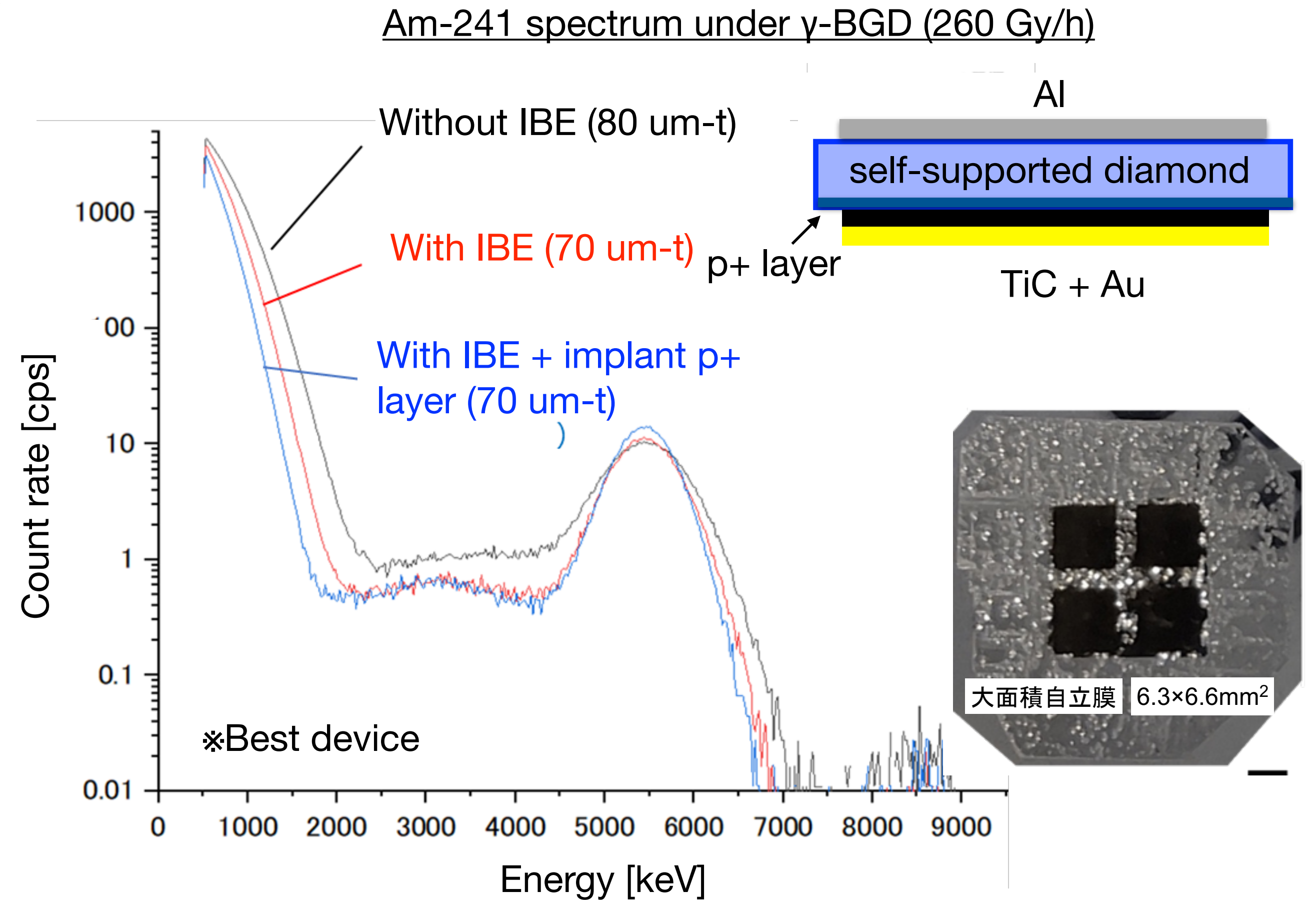
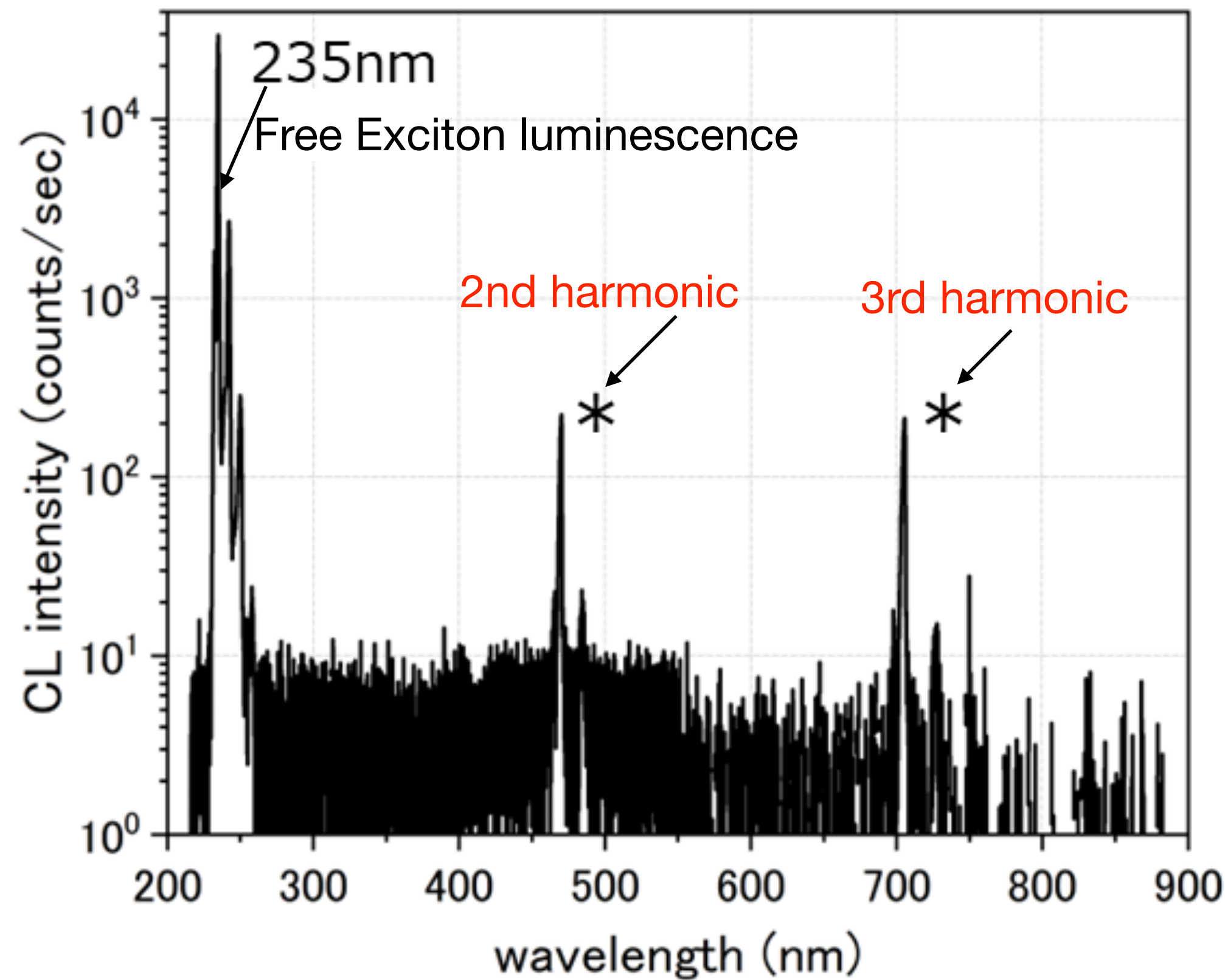


Long process time is covered by parallel CVD machines by venture company.



# Characteristics of the diamond device

- Cathode luminescence method, free-exciton recombination line@ 235nm
- IBE (Ion Beam Etching) on 10 um surface to mitigate roughness
- Implant p+ layer on Ohmic side

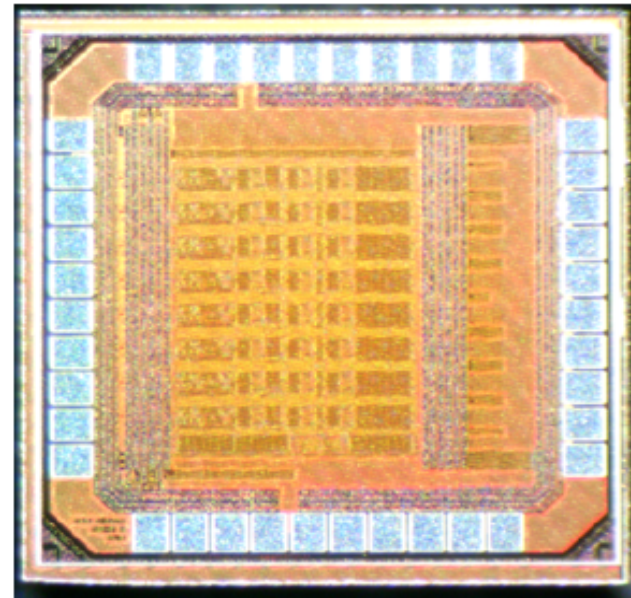


$\gamma$ -rejection capability increased by IBE and p+ layer.

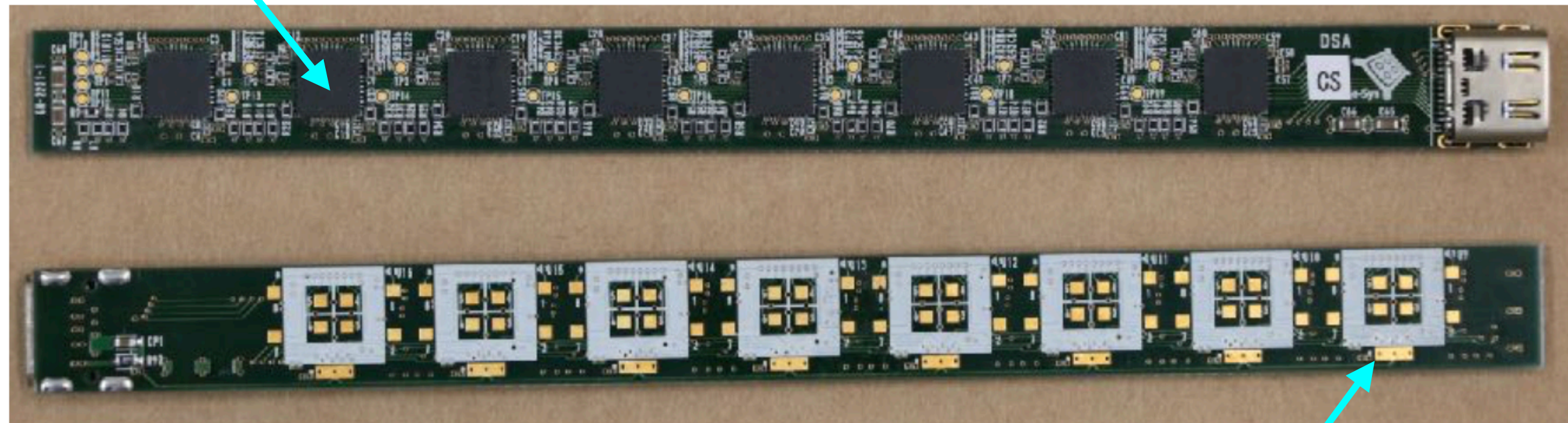


# Analog front-ends & prototype

- TSMC 65 nm LP process, 1 mm x 1 mm
- 8 channels, CSA+CR-RC+Disc.+counter
- No ENC degradation confirmed @ 1 MGy

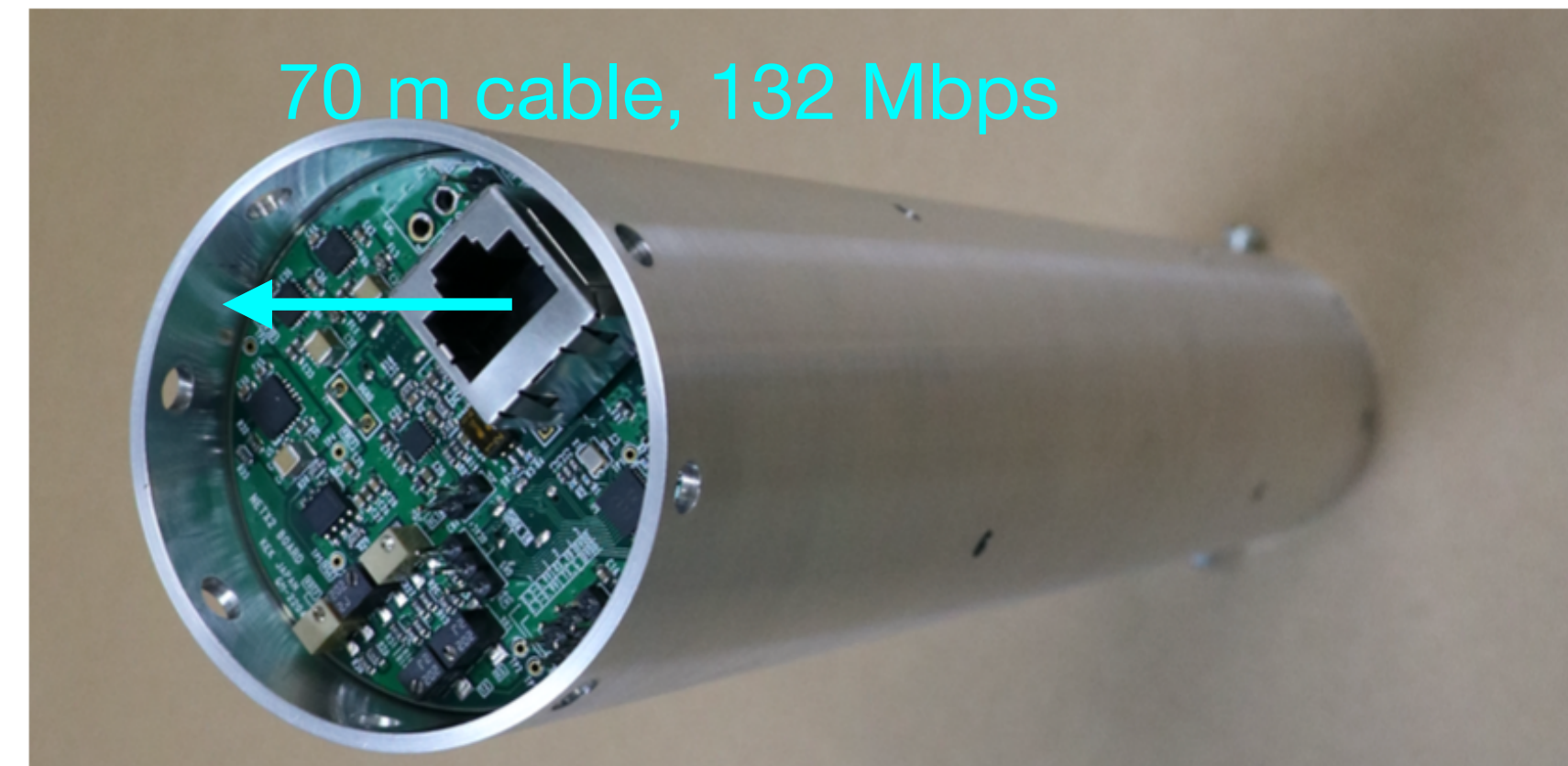
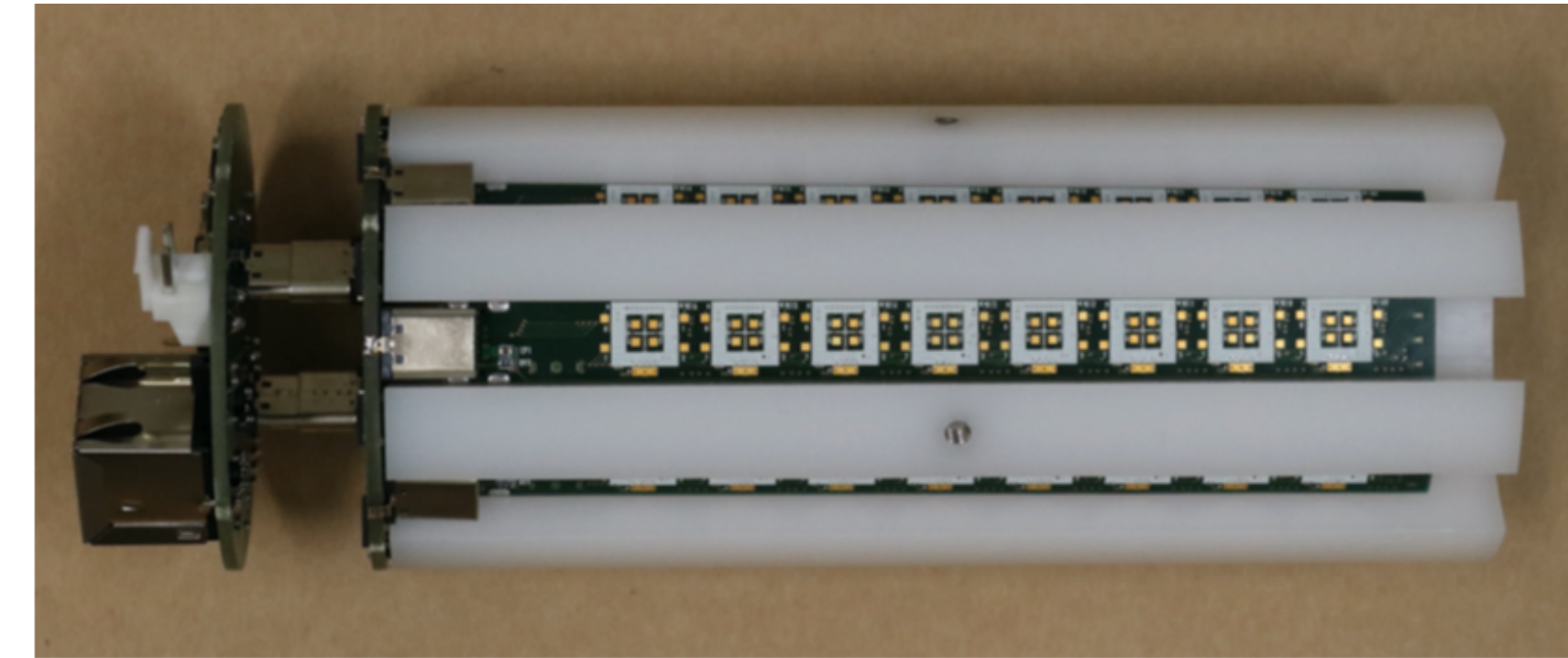


Nu-K_CSA (0.5 mW/ch)	
Type	charge sensitive
Peaking time	50nsec( $t_w \sim 100$ nsec)
Noise	<b><math>\sim 1500e</math> @Cdet=5pF</b>
S/N	$\sim 350$ @Cdet=5pF



Sensor pads (4ch x 600 chips!)

## Prototype of the neutron detector

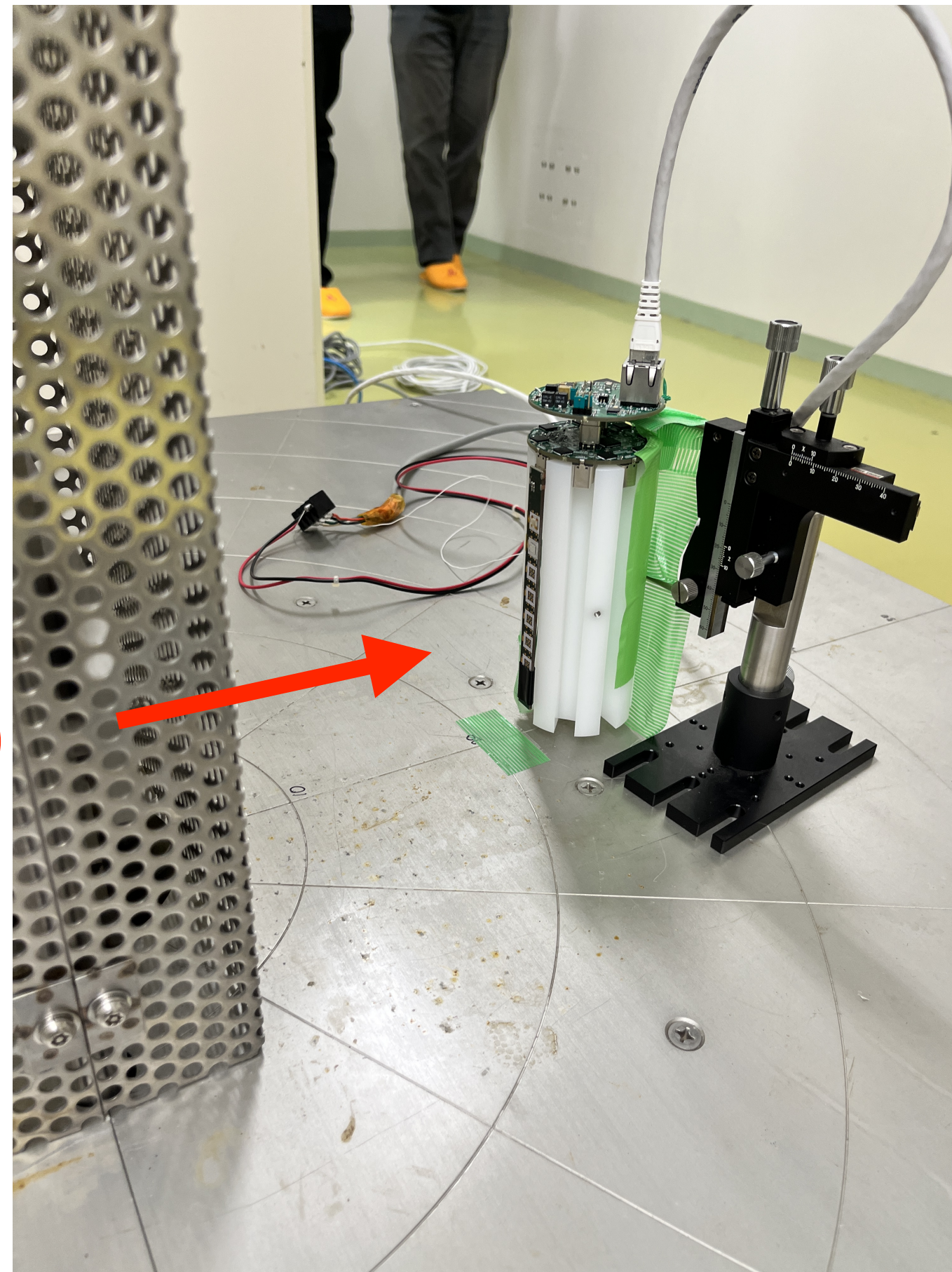




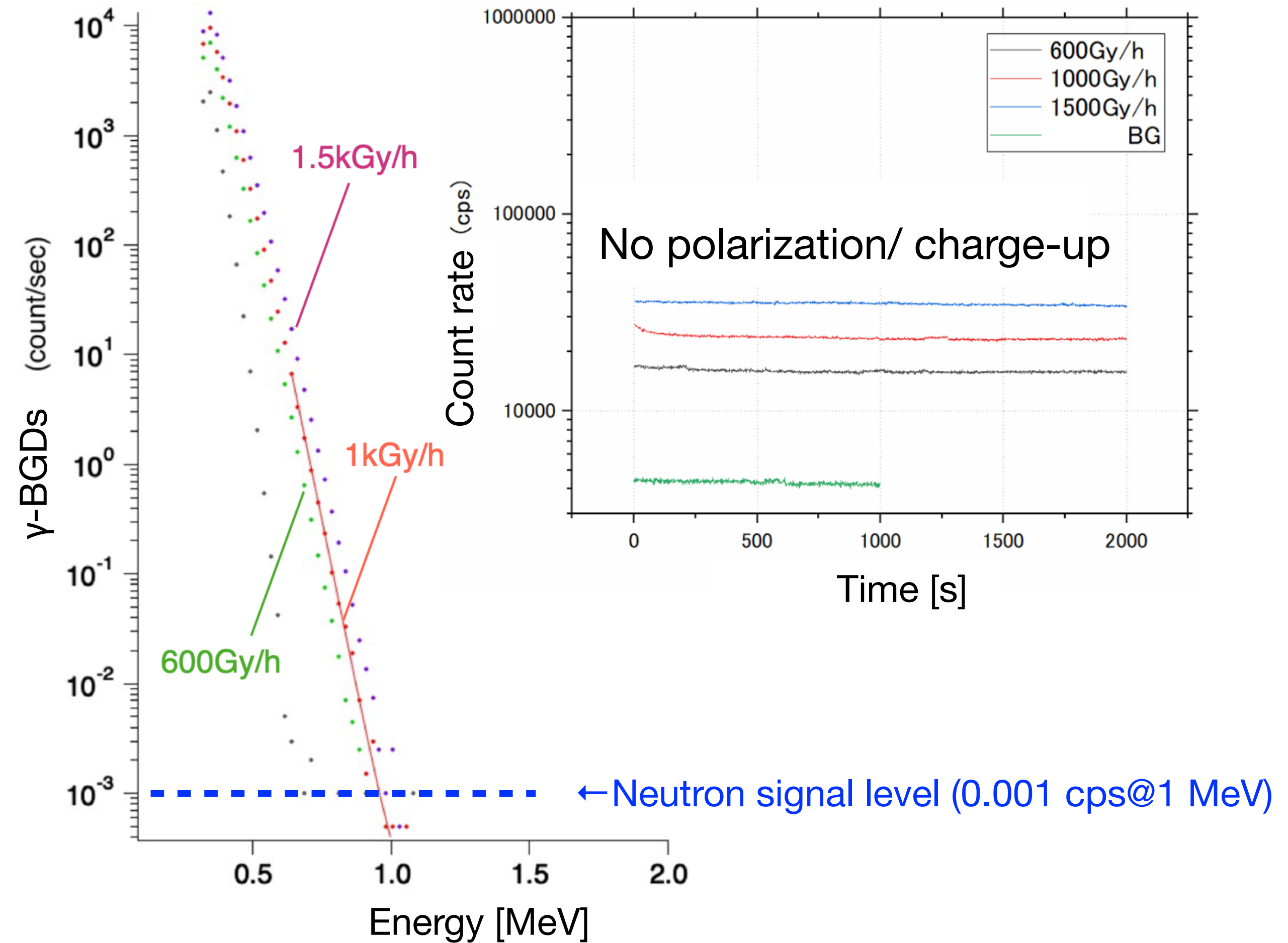
# System test @ $\gamma$ -facility

- Tested best device under  $\gamma$ -BGDs, 1 kGy/h is the requirement
- Neutron converters under preparation

Co-60



$\gamma$ -ray response of the AFF (CSA)



Readout system meets all requirement and we start to develop actual detector from this October.



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**Thank you very much for your attention.**